

EFRC TUTORIAL

Part II:

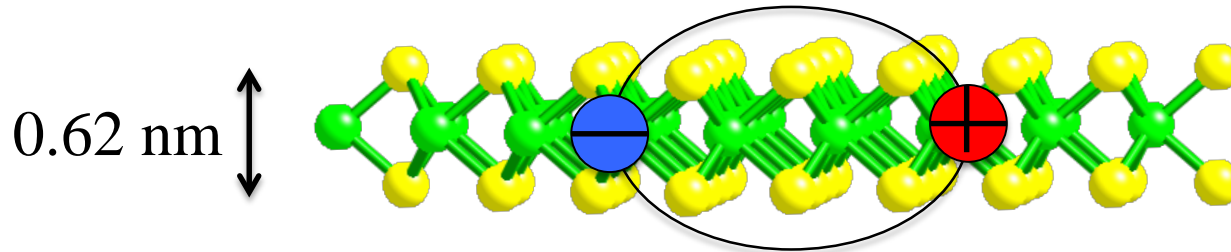
Excitons in 2D TMDC Materials

Linyou Cao

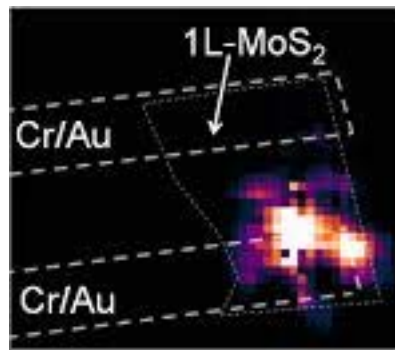
Department of Materials Science and Engineering, North
Carolina State University

Temple University, July 29, 2016

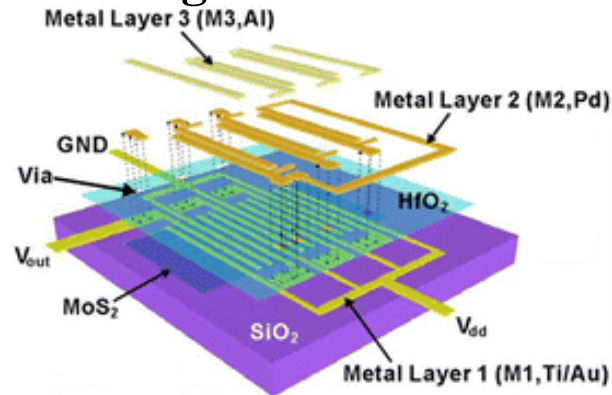
2D TMDC Materials : A Remarkable Excitonic System



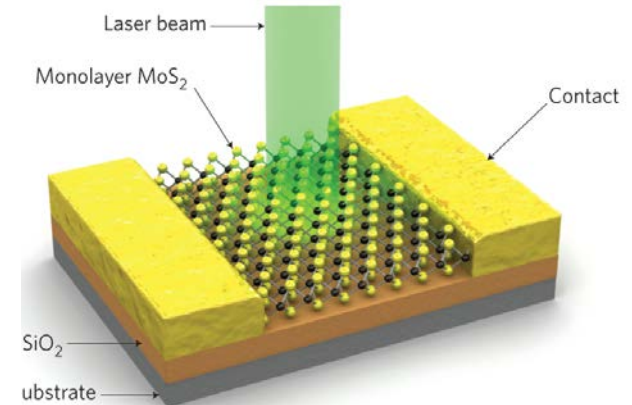
LEDs



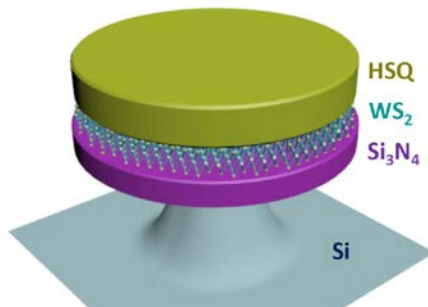
Integrated Circuits



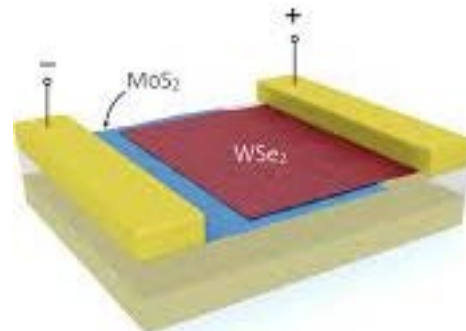
Photodetectors



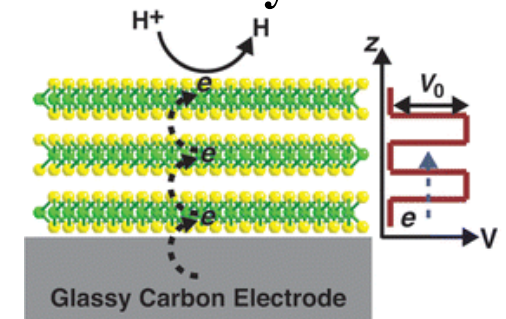
Lasers



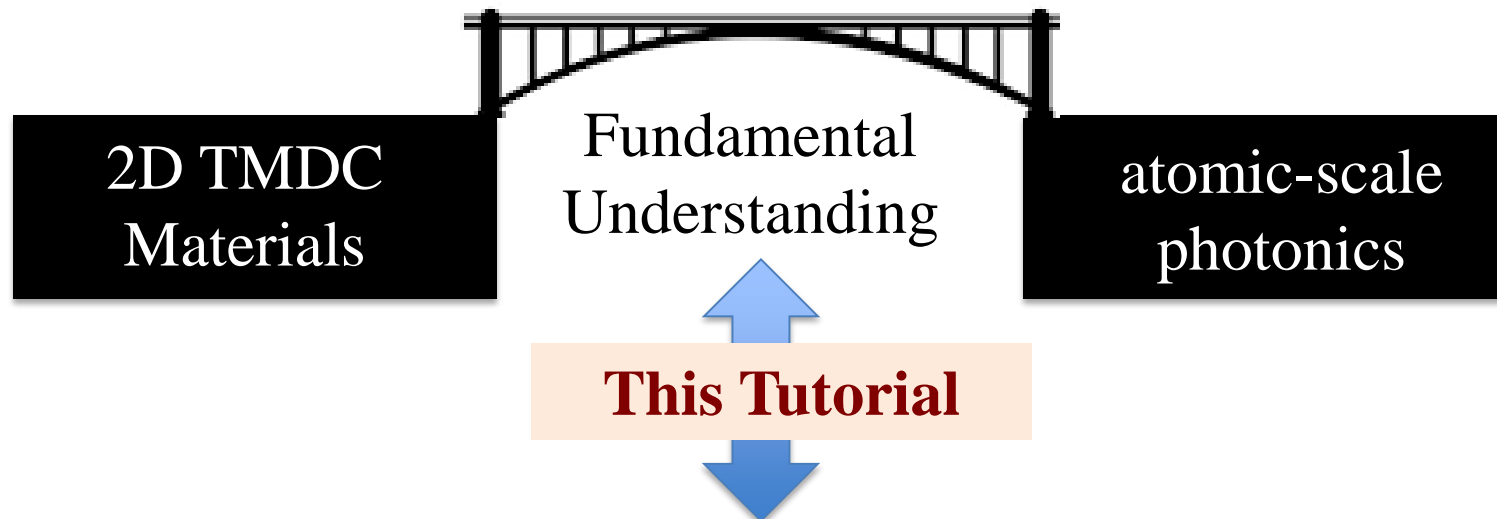
Chemical/bio Sensors



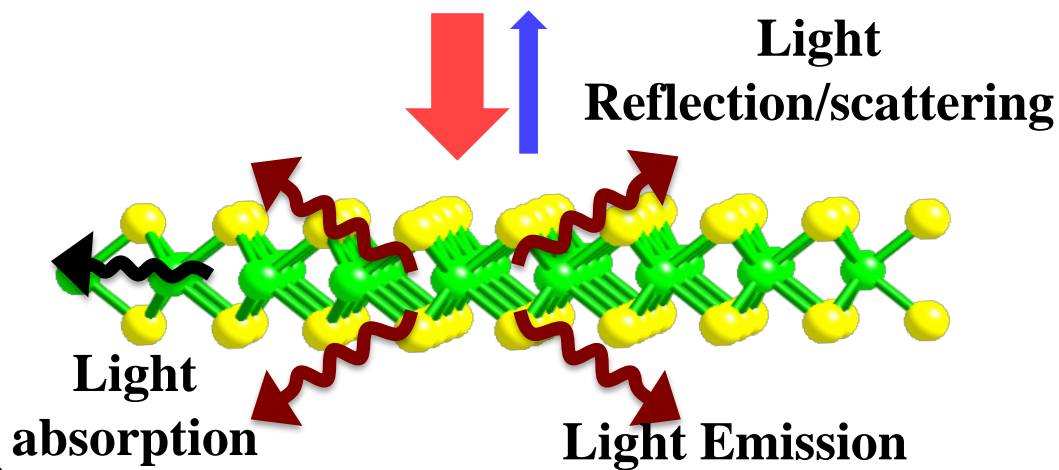
Catalysts



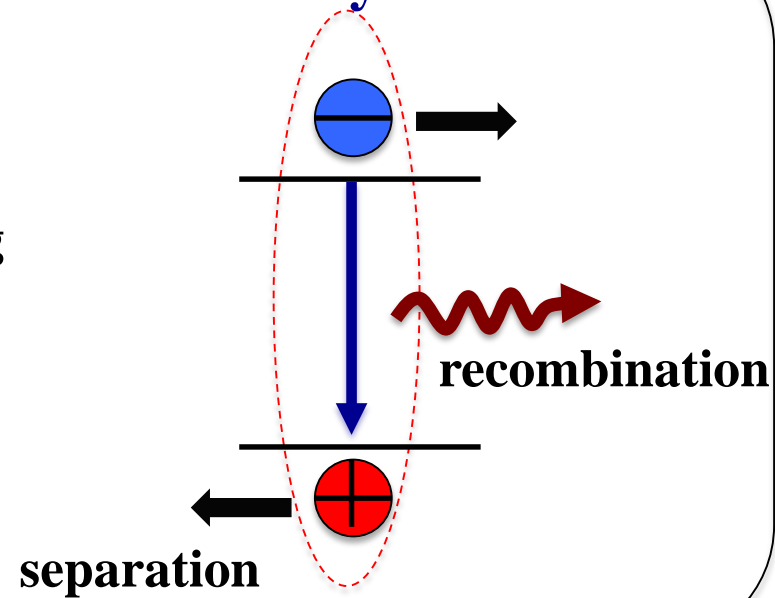
Key: Fundamental Understanding



Light-Matter Interactions

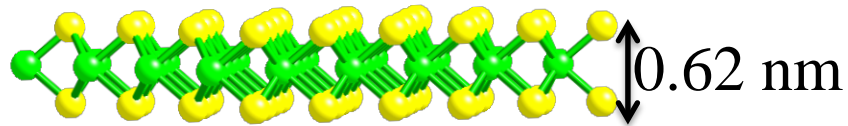


Exciton Dynamics

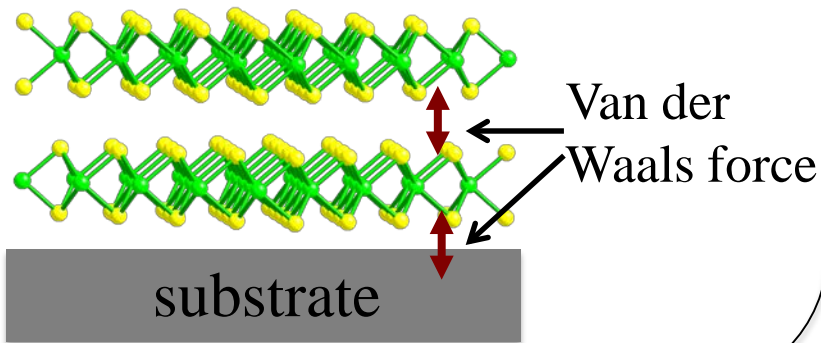


Unique Physical Features → Exotic Excitonic Properties ?

Atomically thin



Weak interaction (vdW)



Strong exciton binding energy

Strong many-body interactions

High susceptibility to substrate effects

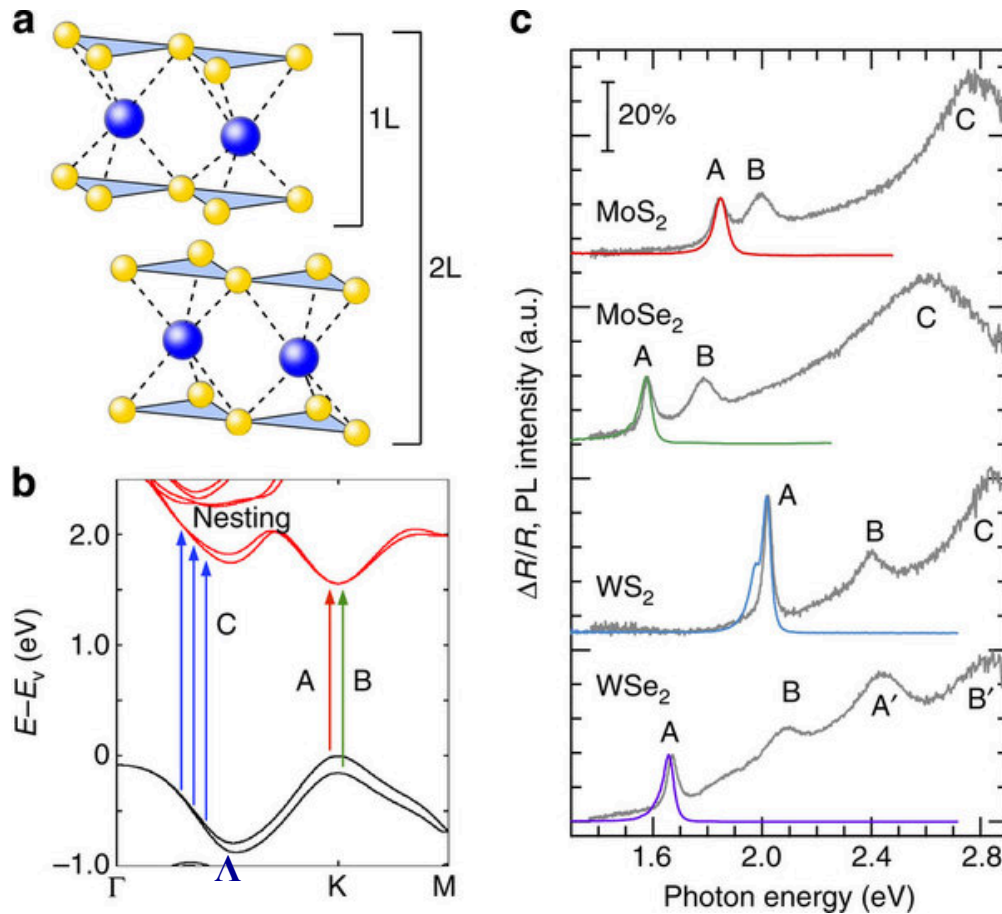
Dominating excitonic effects in light-matter interactions

Efficient interfacial transfer

Overview

- 1. Excitonic States, Binding Energy, Exciton Radius**
- 2. Many body interactions (Coulomb scattering)**
Exciton-charge, exciton-exciton
- 3. Effect of substrates**
- 4. Exciton dynamics**
- 5. Dominating excitonic effects in light-matter interactions**

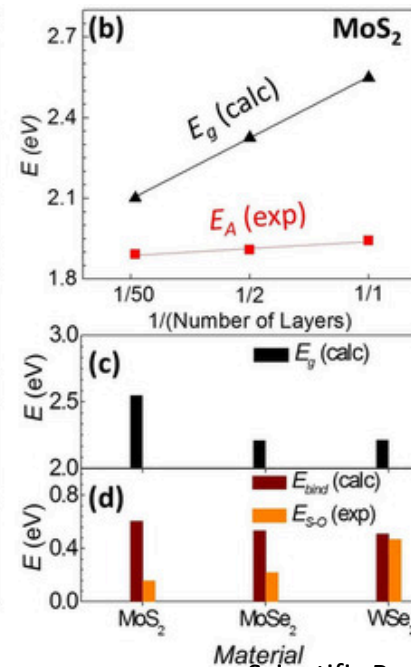
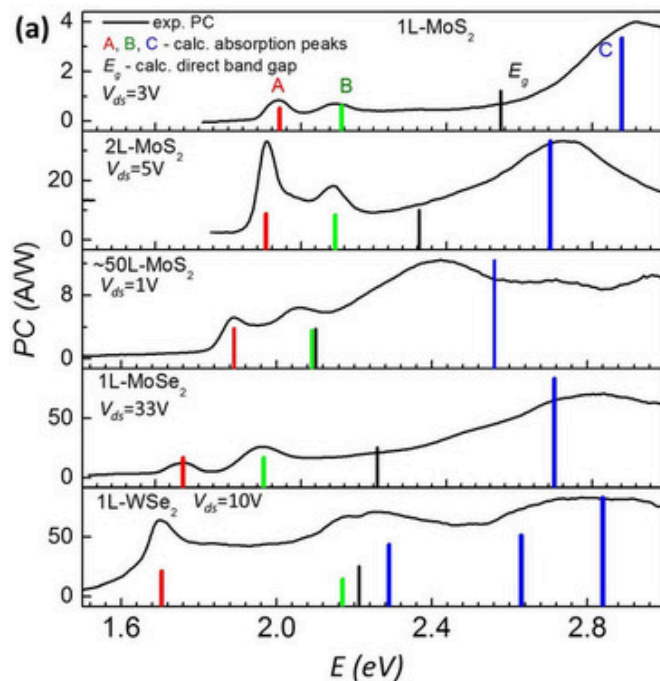
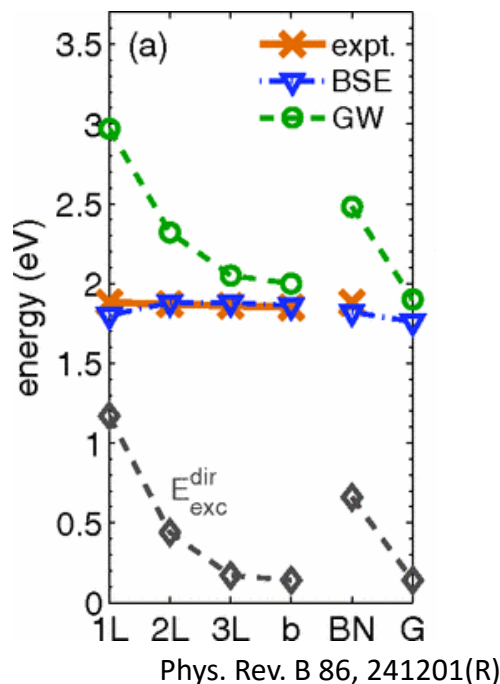
Excitonic States



Nature Communications 5, 4543, (2014)

A and B from interband transition of K/K' points, and C from transition in the Brillouin zone between Γ and Λ

Extraordinarily Strong Binding Energy

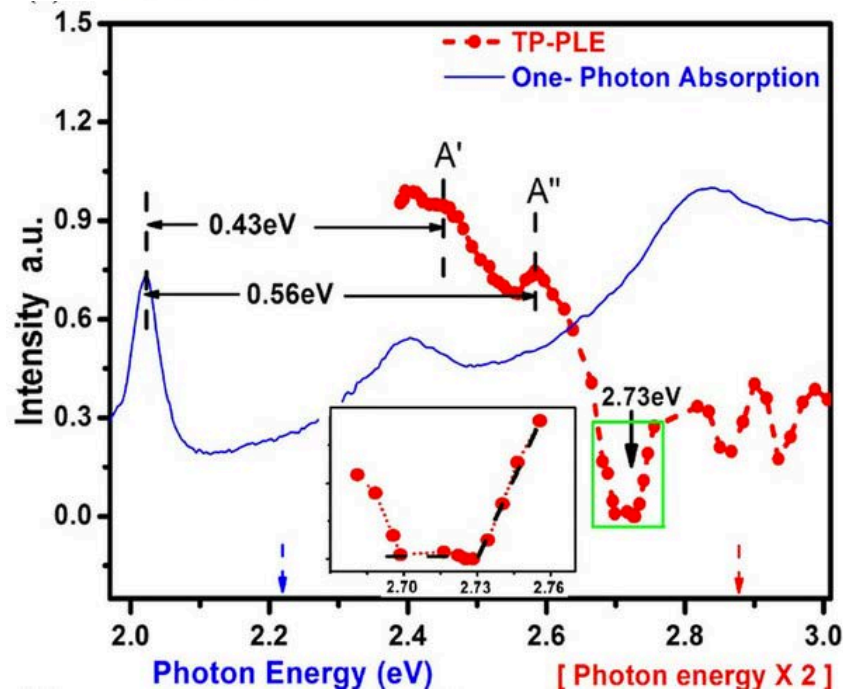
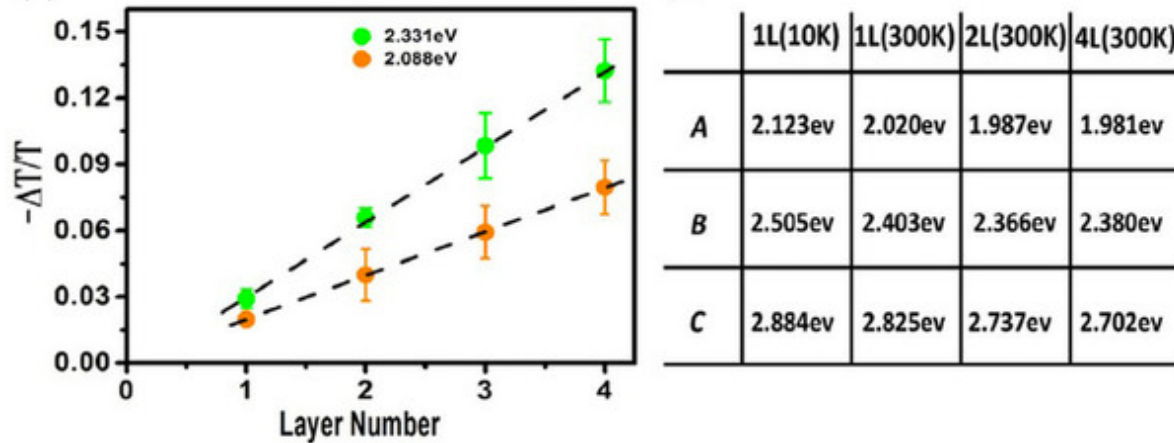


Scientific Reports 4, 6608, 2014

	Energy cutoffs	k point	E_g	E_g (optical)	Binding energy
Monolayer MoS ₂ (3.160 Å)	400 and 200	$6 \times 6 \times 1$ (SOC)	2.89	1.87	1.02
		$6 \times 6 \times 1$	2.99	1.96	1.03
		$9 \times 9 \times 1$	2.84	2.08	0.76
		$12 \times 12 \times 1$	2.78	2.16	0.62
		$15 \times 15 \times 1$	2.76	2.22	0.54
Monolayer MoS ₂ (3.190 Å)	600 and 300	$12 \times 12 \times 1$	2.80	2.17	0.63
		$12 \times 12 \times 1$	2.66	2.04	0.62
Monolayer WS ₂ (3.155 Å)	400 and 200	$6 \times 6 \times 1$ (SOC)	3.02	1.97	1.05
		$6 \times 6 \times 1$	3.28	2.21	1.07
		$9 \times 9 \times 1$	3.12	2.34	0.78
		$12 \times 12 \times 1$	3.06	2.43	0.63
		$15 \times 15 \times 1$	3.05	2.51	0.54
Monolayer WS ₂ (3.190 Å)	600 and 300	$12 \times 12 \times 1$	3.11	2.46	0.65
		$12 \times 12 \times 1$	2.92	2.28	0.64

The exciton binding energy in 1L MoS₂ is reported ~ 0.4-1.1 eV (0.4-0.6 eV more reasonable)

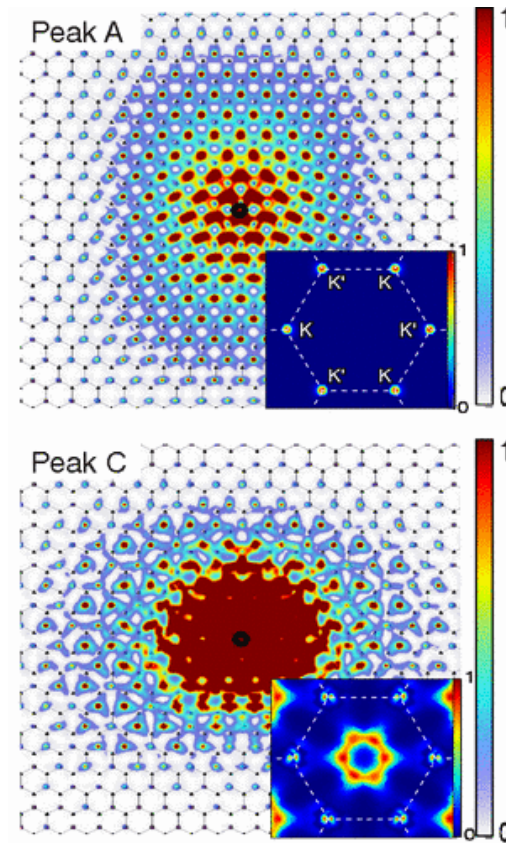
Strong Binding Energy in WS2



Scientific Reports 5, 9218 (2015)

The exciton binding energy in WS2 monolayer is 0.71 ± 0.01 eV around K valley

Exciton Radius

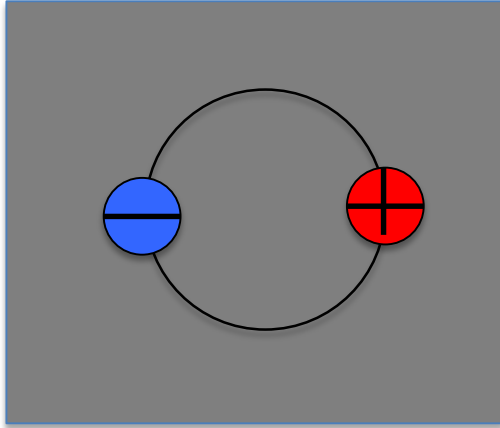


Phys. Rev. Lett. 111, 216805

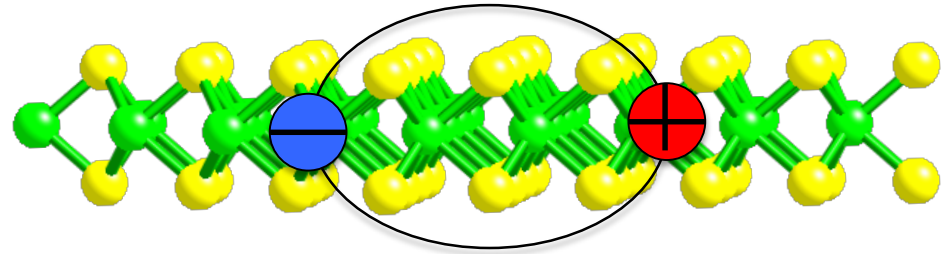
The exciton radius is estimated to be 0.5-2 nm

Anisotropy: Fractional Dimensional Space

Conventional materials: Isotropic



2D TMDC materials: Anisotropic



How should the concept developed for isotropic systems be adjusted for the extremely anisotropic excitons in 2D TMDC materials?

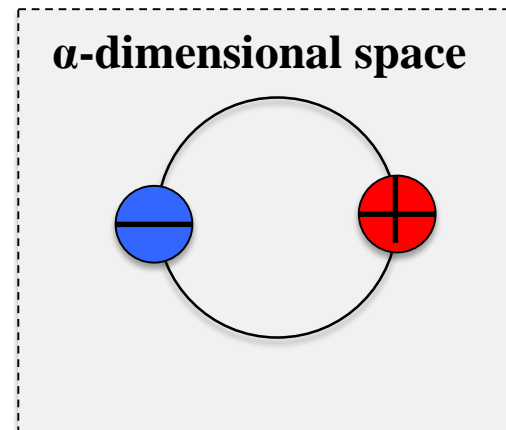
Fractional dimensional space model

$$\alpha = (E_{\text{bulk}}/E_{\text{2D}})^{1/2} + 1$$

X.-F. He, Physical Review B **42**, 11751 (1990).

C. Tanguy, Physical Review Letters **75**, 4090 (1995).

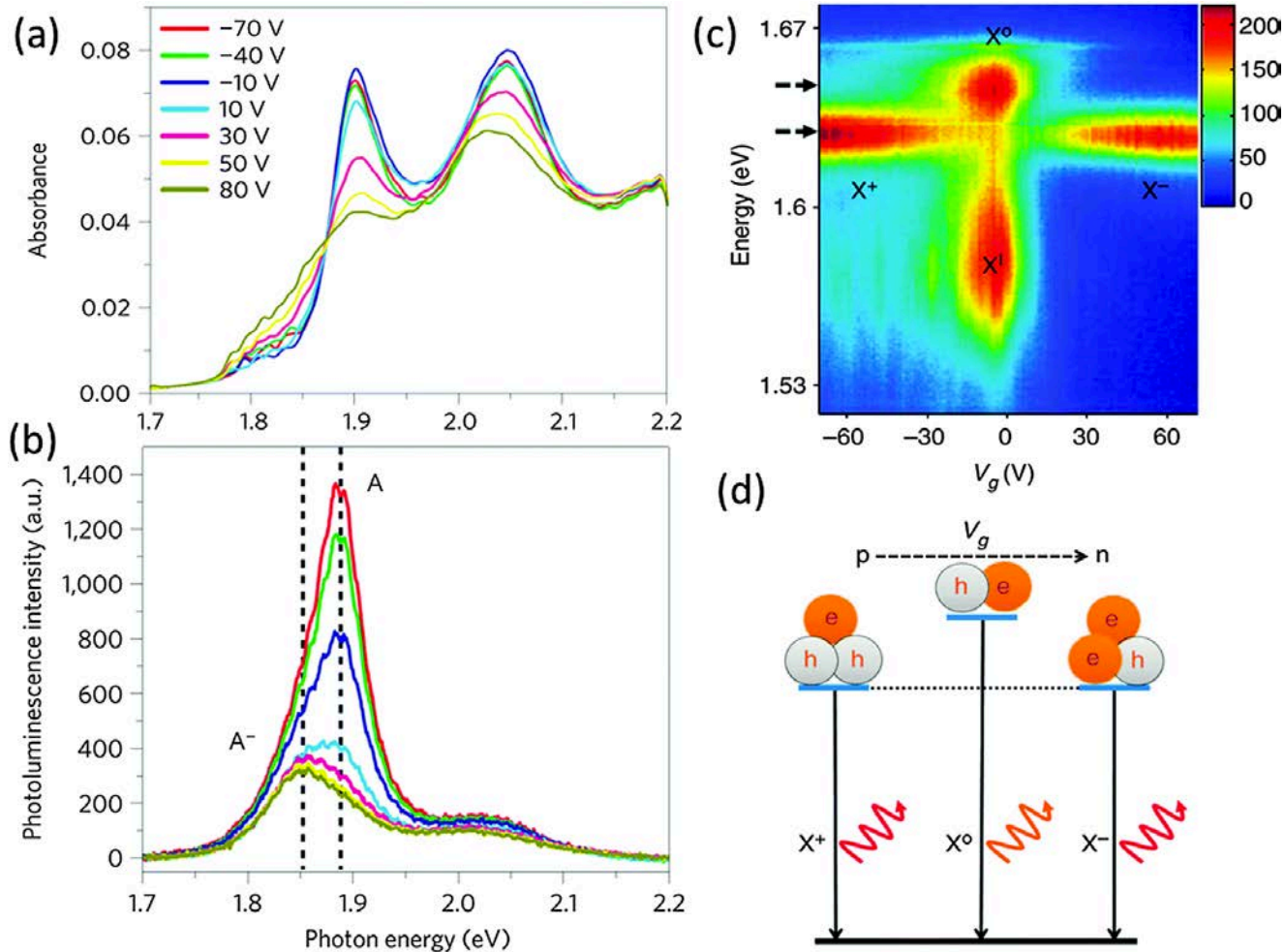
C. Tanguy, P. Lefebvre, H. Mathieu, and R. J. Elliott, Journal of Applied Physics **82**, 798 (1997).



Many-body Interactions

- **Exciton-charge**
- **Exciton-exciton**

Exciton-Charge Interaction: Neutral and Charged Excitons

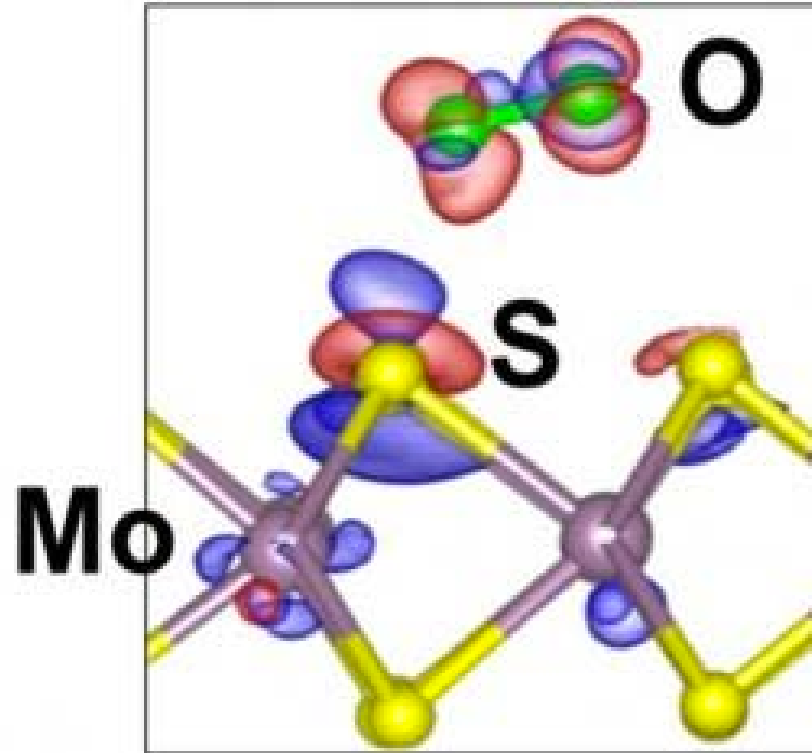
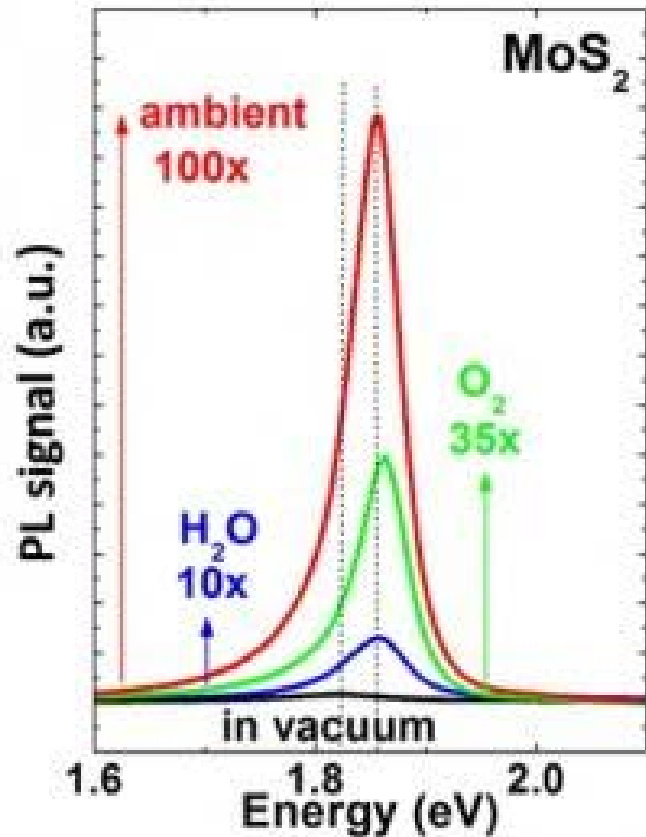


Nature Materials 12, 207–211 (2013)

Nature communication, Xiaodong Xu' group

Trions have a binding energy estimated to be ~ 20 meV and much lower efficiency than neutral excitons

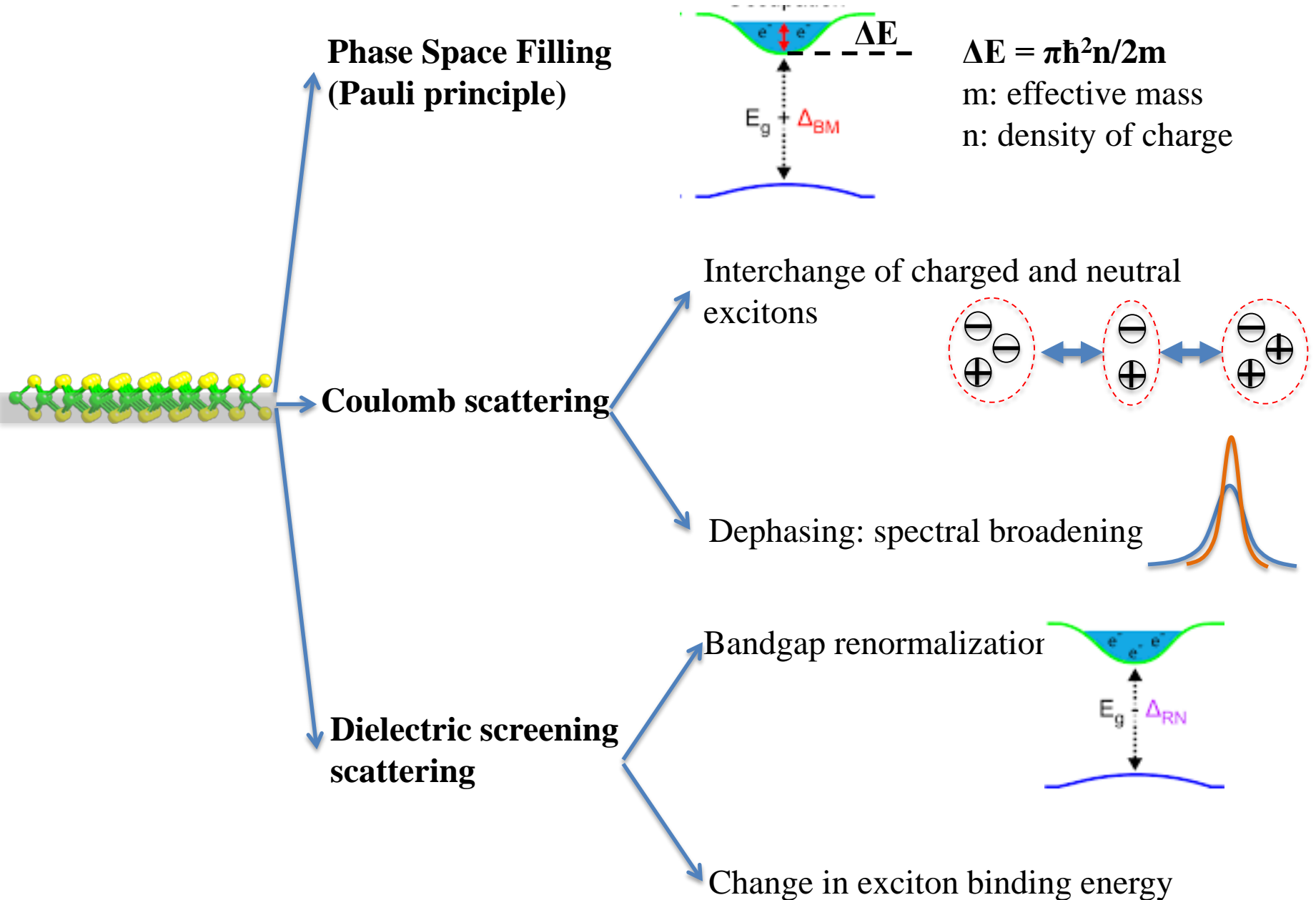
Effect of Doping on Luminescence Efficiency



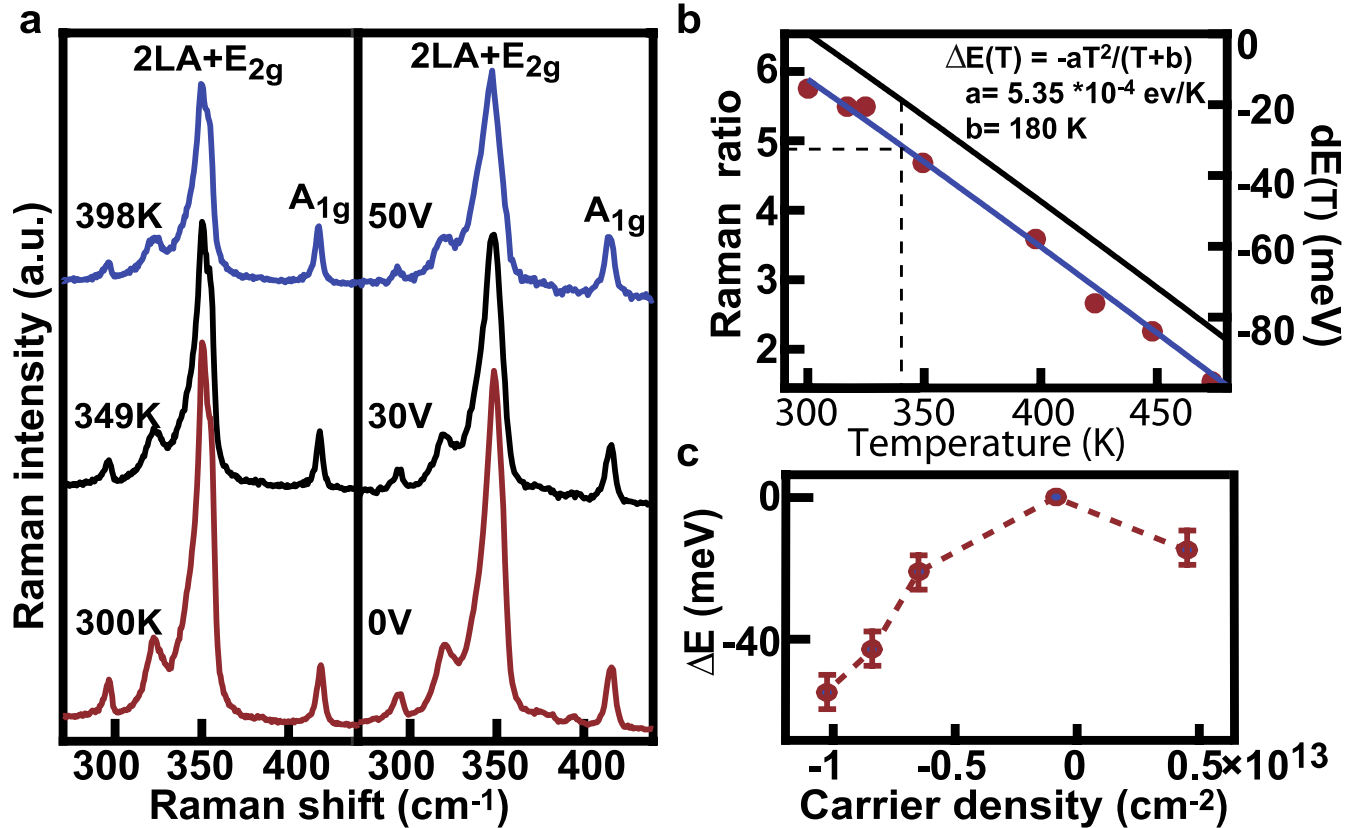
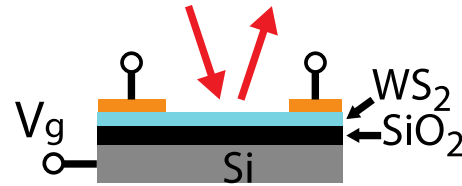
Nano Lett., 2013, 13 (6), pp 2831–2836

The PL intensity and position can be substantially affected by the doping level

Doping Effect: More than Coulomb Scattering

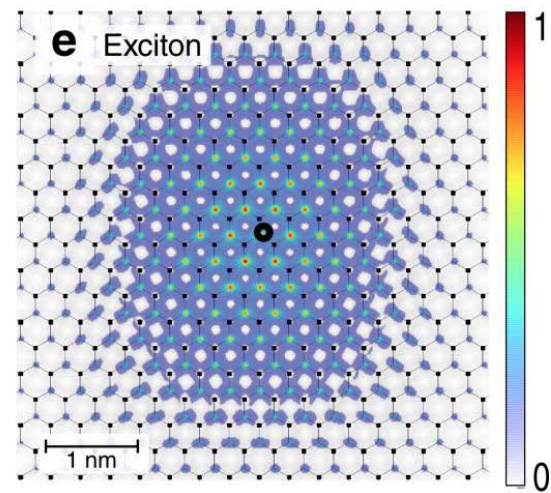
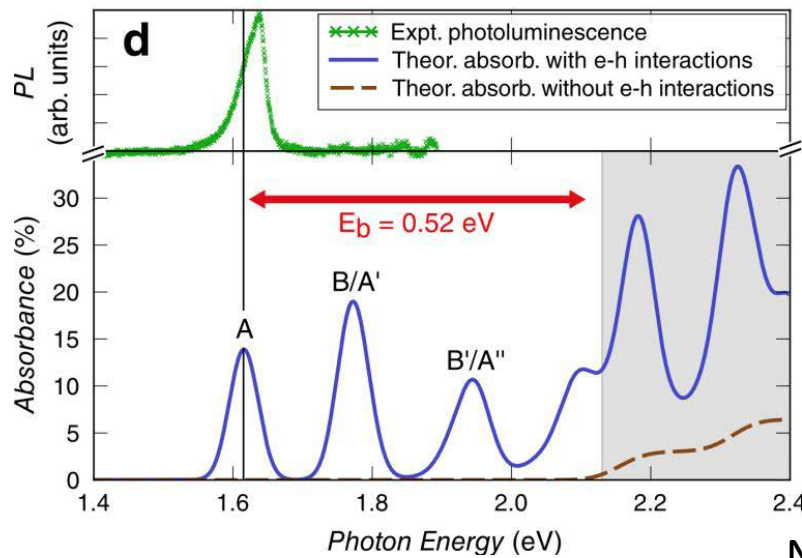
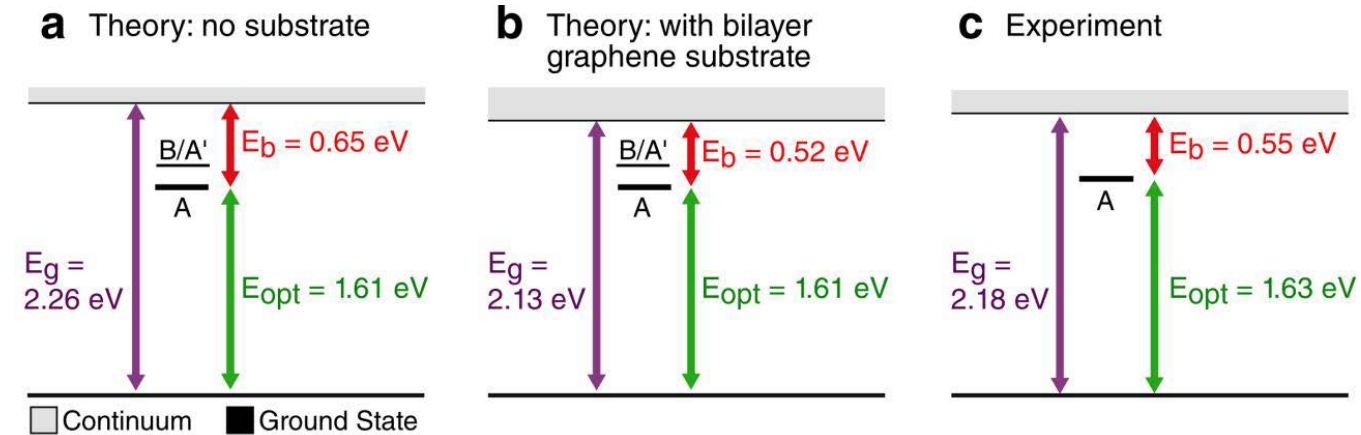


Bandgap Renormalization by Dielectric Screening



The electronic bandgap can be renormalized due to the dielectric screening effect of doping.

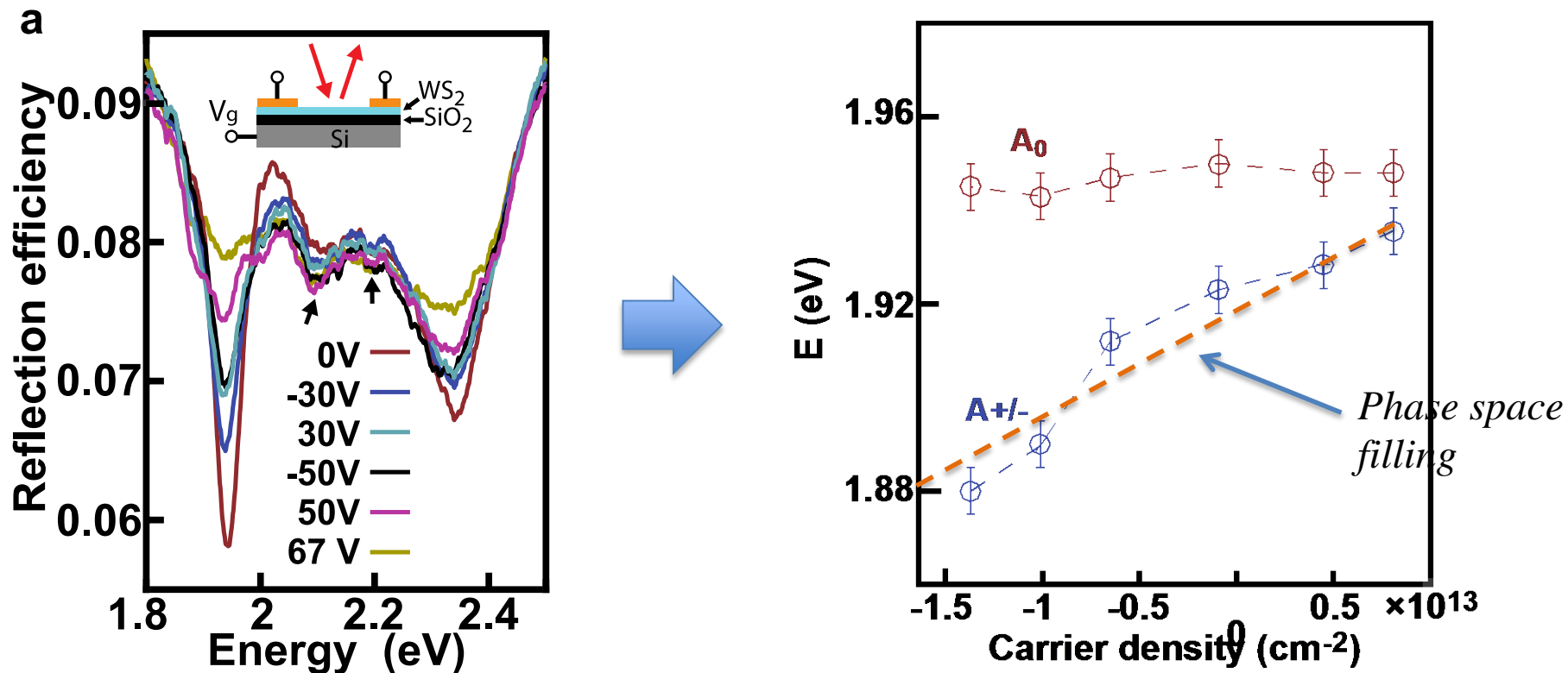
Bandgap Renormalization by Dielectric Screening



Nature Materials 13, 1091–1095 (2014)

The electronic bandgap can be renormalized due to the dielectric screening effect of substrates (but the value is most likely overestimated).

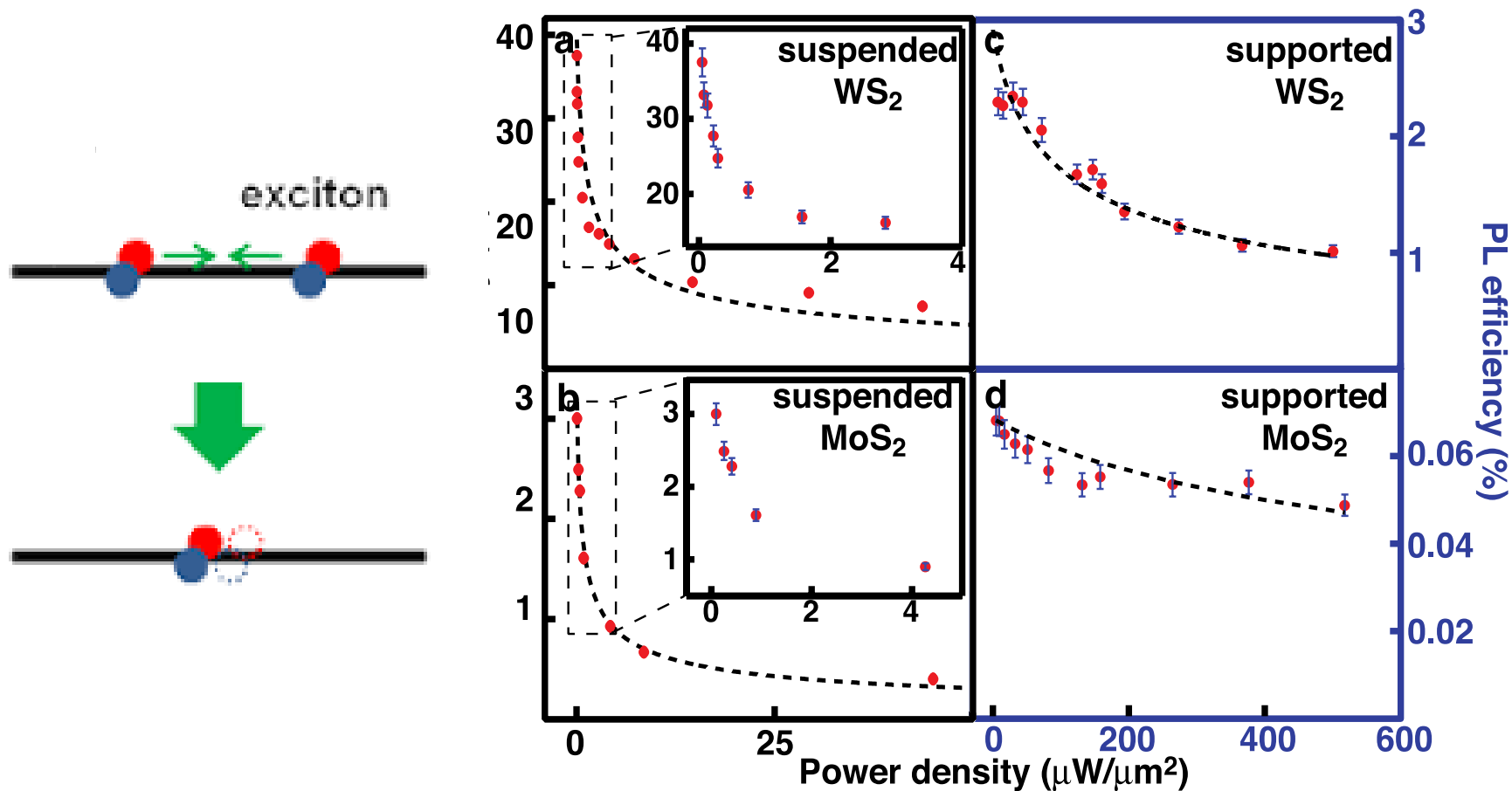
Change in Exciton Binding Energy by Dielectric Screening



change in binding energy $\Delta E_{\text{ex}} = \Delta E_{\text{g}} - \Delta E_{\text{opt}}$,
 ΔE_{g} : bandgap renormalization, ΔE_{opt} change in optical bandgap

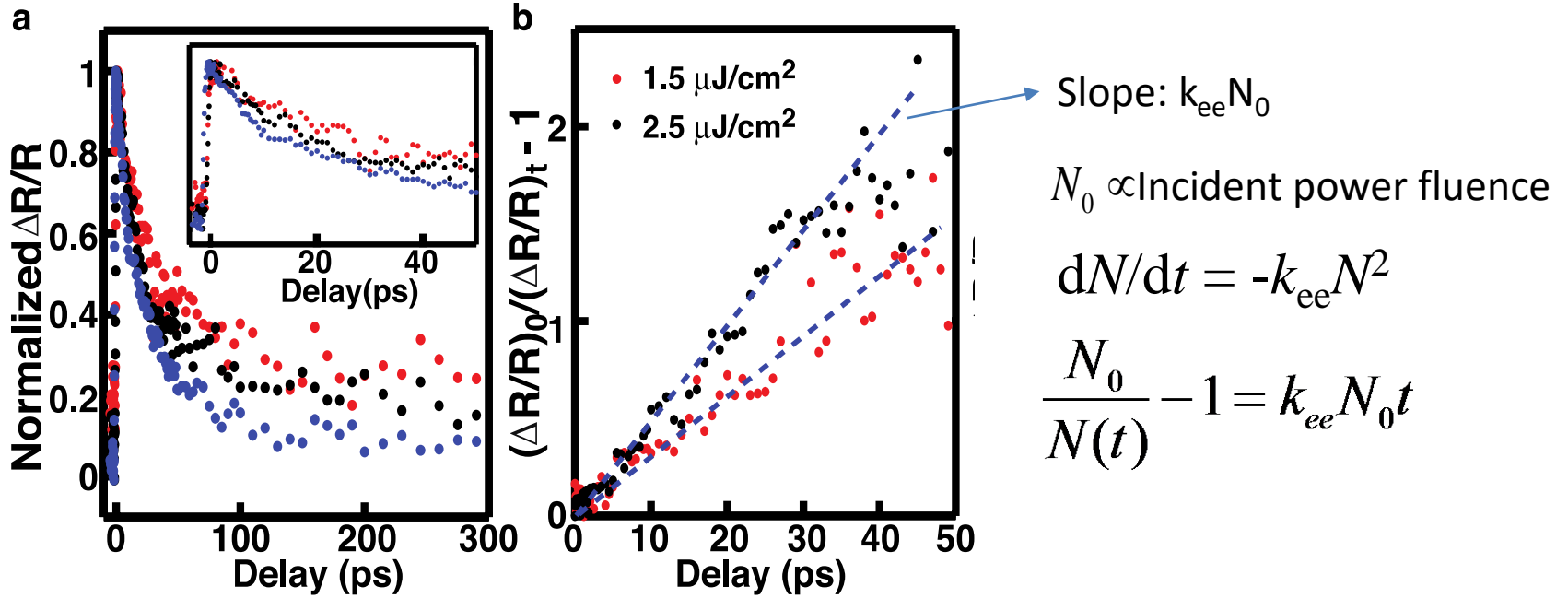
Change in exciton binding energy: 5- 25 meV

Exciton-Excitons Annihilation



High exciton-exciton annihilation rate!

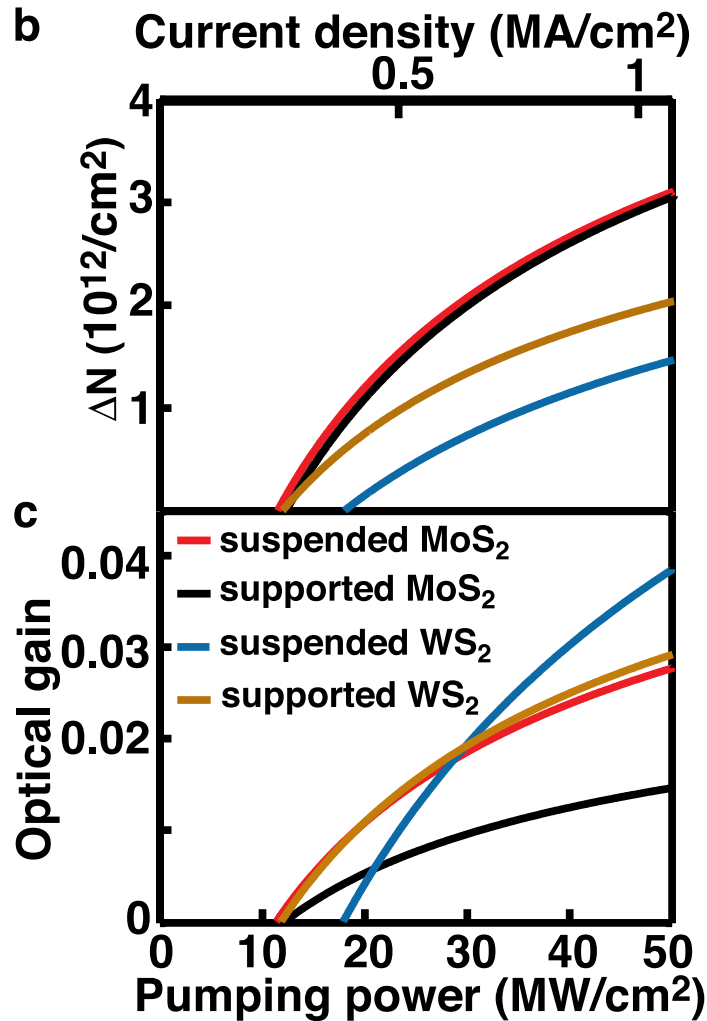
Exciton-Exciton Annihilation



	k_{ee} (cm ² /s)	τ_r (ns)	τ_{nr} (ns)
Suspended WS ₂	0.3	1	0.76
As-grown WS ₂	0.1	4.5	0.13
Suspended MoS ₂	0.1	28	1
As-grown MoS ₂	0.05	80	0.05

Dependence of exciton-exciton annihilation rate on substrates

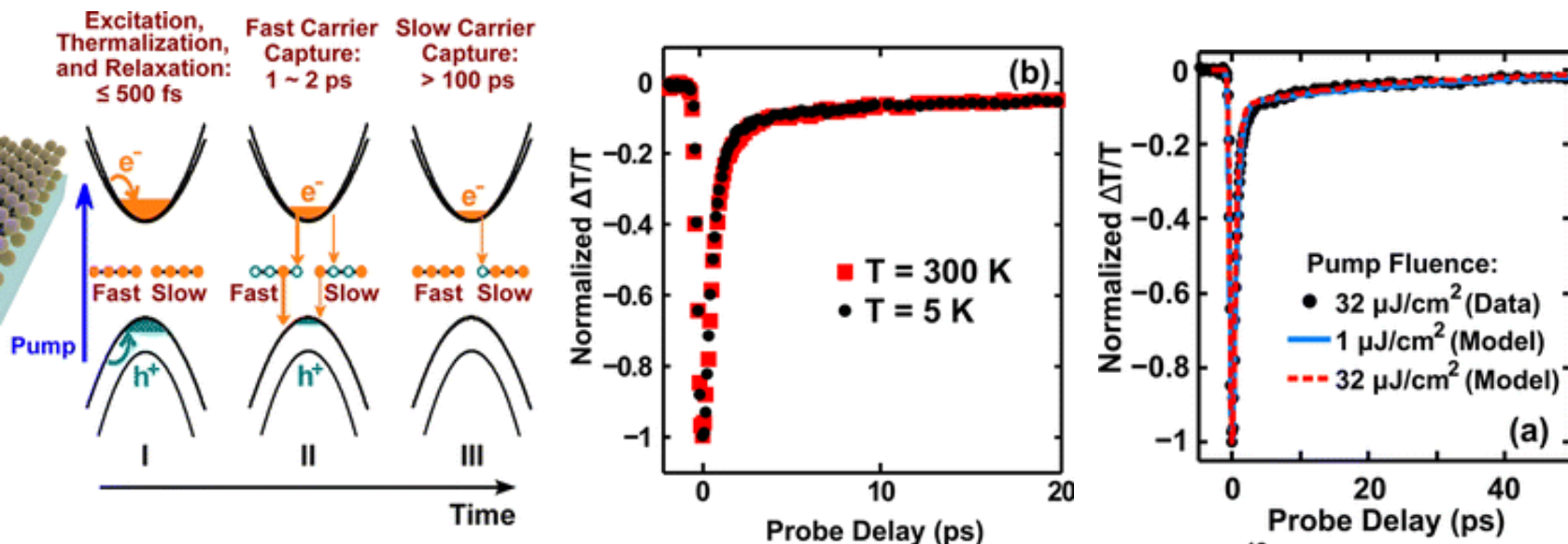
Pumping Threshold for Population Inversion



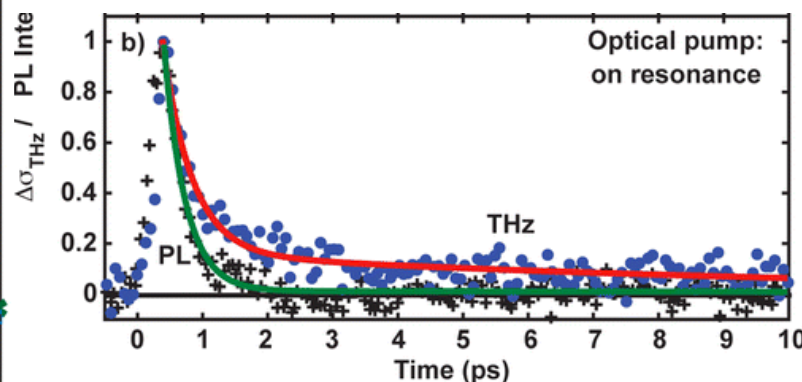
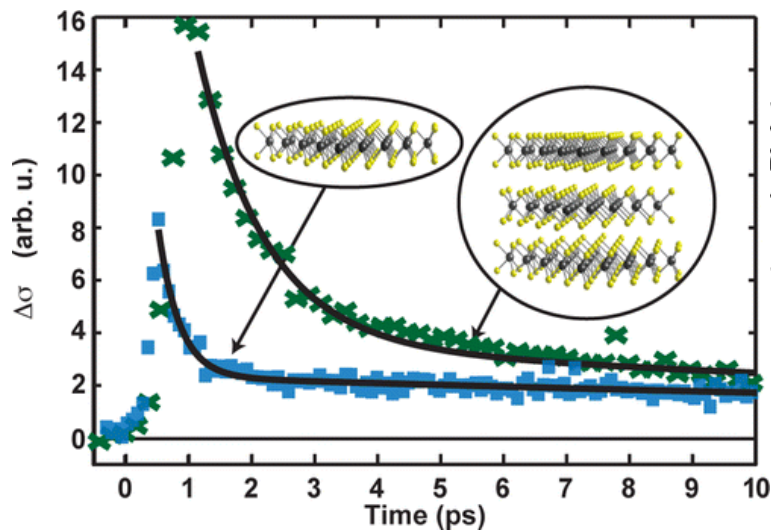
$$\frac{dN}{dt} = -\left(\frac{1}{\tau_r} + \frac{1}{\tau_{nr}}\right)N - k_{ee}N^2 + \alpha I_0$$

The pumping threshold is solely dictated by the exciton-exciton annihilation rate.

Exciton Dynamics: Defect-assisted



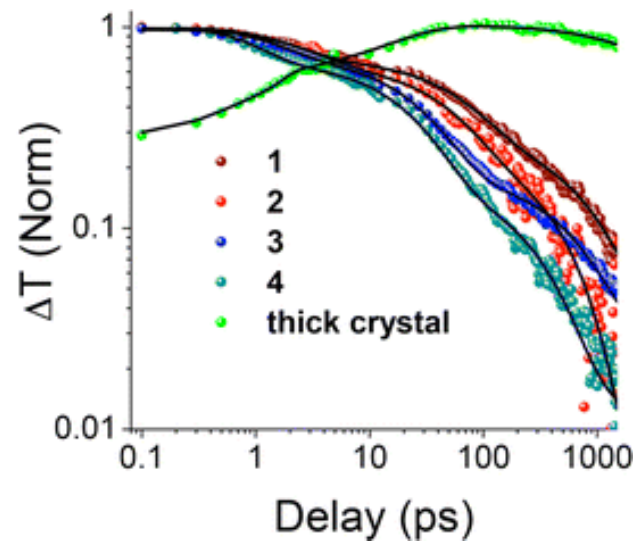
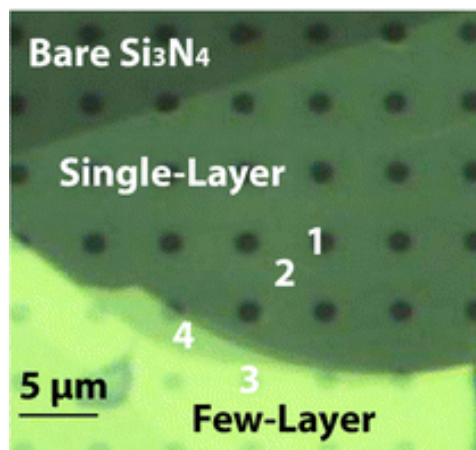
Nano Lett., 2015, 15 (1), pp 339–345



ACS Nano, 2014, 8 (11), pp 11147–11153

Defect-Assisted Electron–Hole Recombination

Exciton Lifetime



	τ_1 (ps)	τ_2 (ps)	τ_3 (ps)
1 (suspended monolayer)	2.6 ± 0.1 (39%)	74 ± 3 (39%)	850 ± 48 (22%)
2 (supported monolayer)	3.3 ± 0.2 (40%)	55 ± 3 (38%)	469 ± 26 (22%)
3 (suspended few-layer)	2.1 ± 0.1 (40%)	34 ± 1 (47%)	708 ± 55 (13%)
4 (supported few-layer)	1.2 ± 0.1 (47%)	29 ± 2 (41%)	344 ± 28 (12%)
thick crystal	1.8 ± 0.6 (19%) (rise)	20 ± 2 (81%) (rise)	2626 ± 192 (100%) (decay)

ACS Nano, 2013, 7 (2), pp 1072–1080

Exciton lifetime in many reports: 1-30ps.

Exciton Lifetime

In most of the current dynamics studies, the process of exciton-exciton annihilation is ignored.

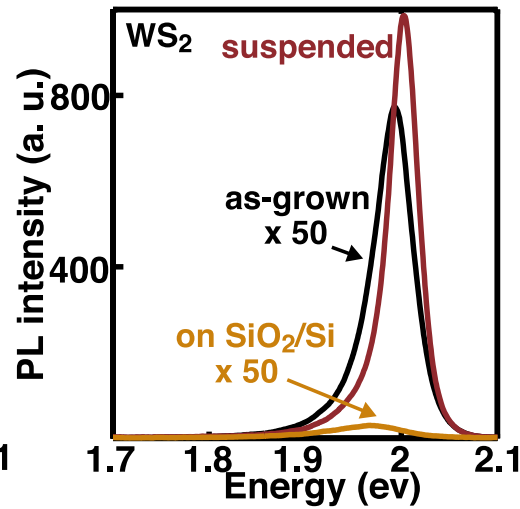
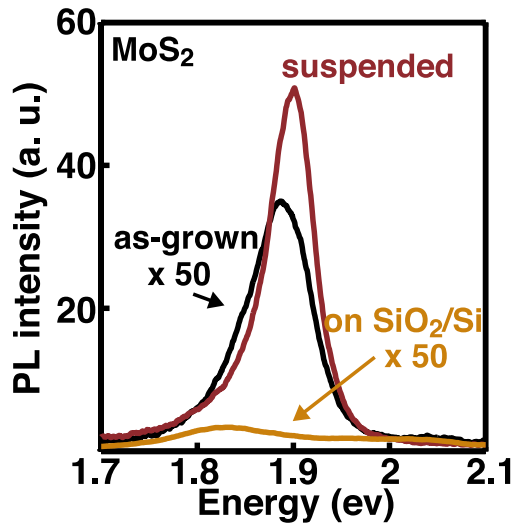
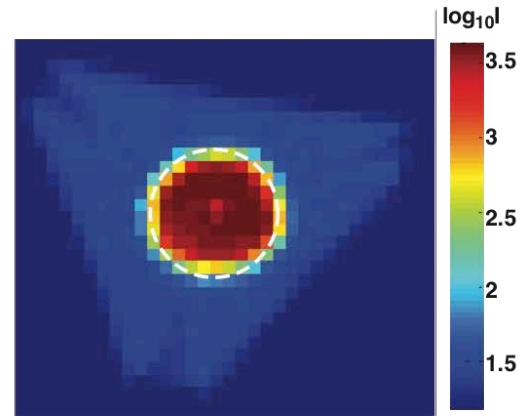
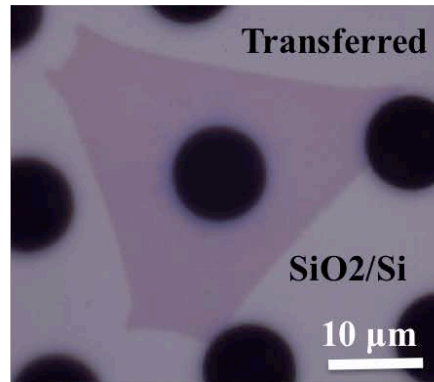
This makes problems in the evaluation for the intrinsic lifetime of excitons

Our result

	k_{ee} (cm ² /s)	τ_r (ns)	τ_{nr} (ns)
Suspended WS ₂	0.3	1	0.76
As-grown WS ₂	0.1	4.5	0.13
Suspended MoS ₂	0.1	28	1
As-grown MoS ₂	0.05	80	0.05

Substrate Effects

Effects of Substrate

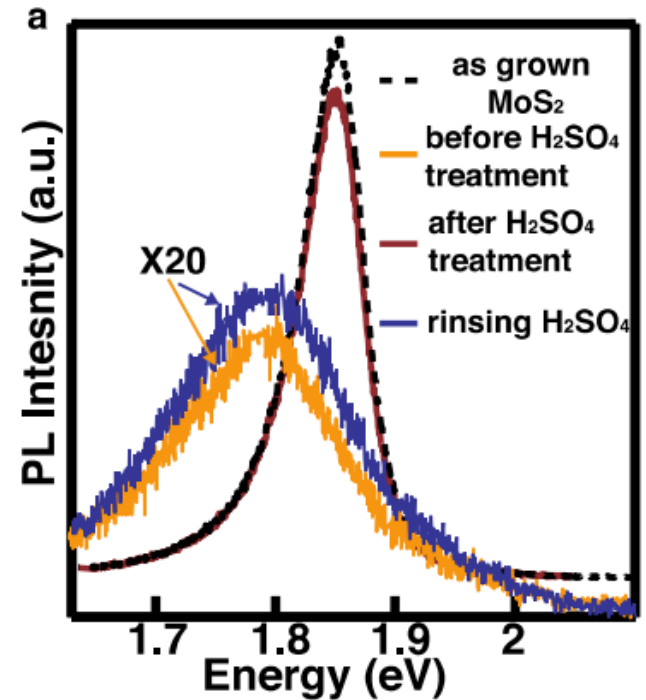
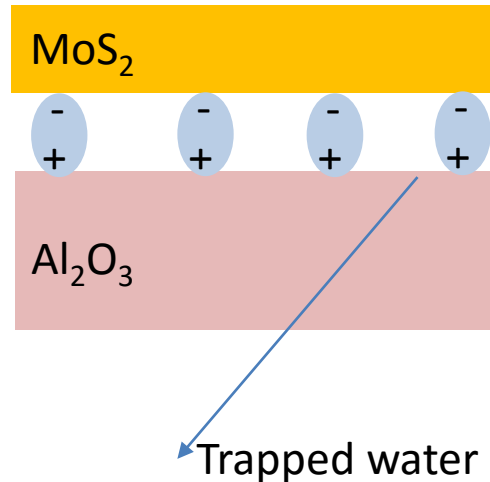
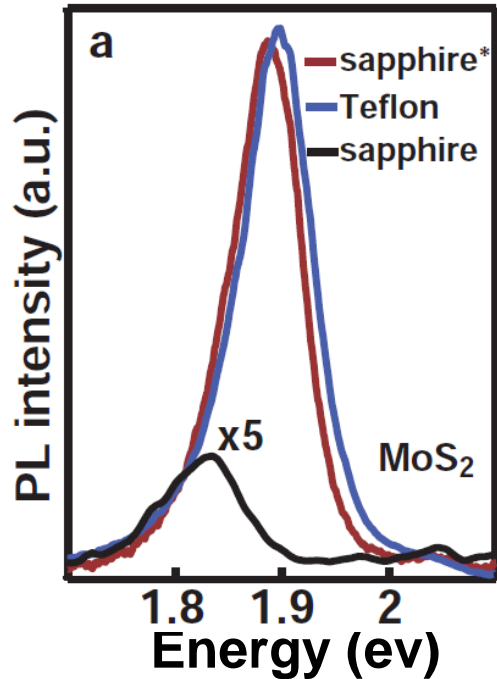


	PL efficiency
As-grown MoS2	0.1%
As-grown WS2	1.5%
Suspended MoS2	3%
Suspended WS2	35%

> 2 orders of magnitude improvement in the PL in suspended monolayers!

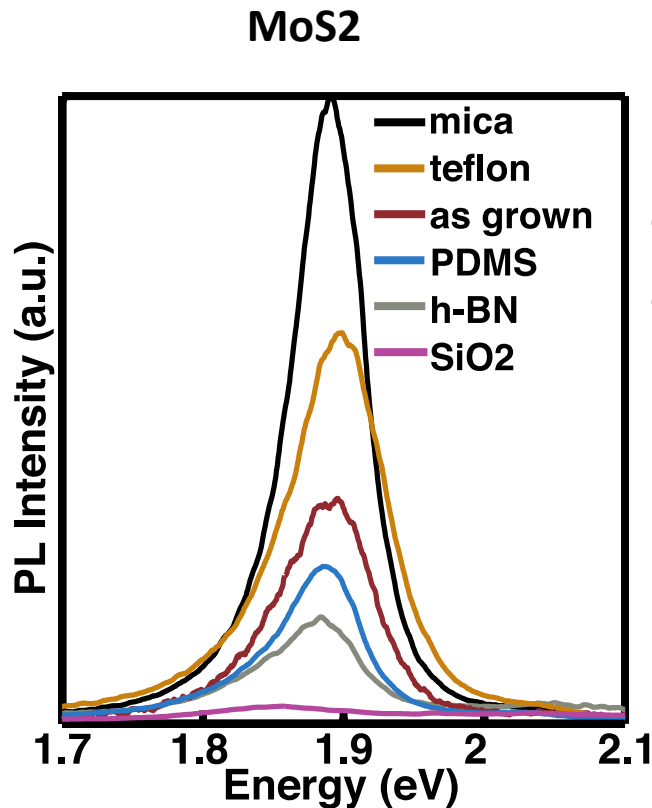
Effect of Trapped Moisture on Hydrophilic Substrates

* denote as grown

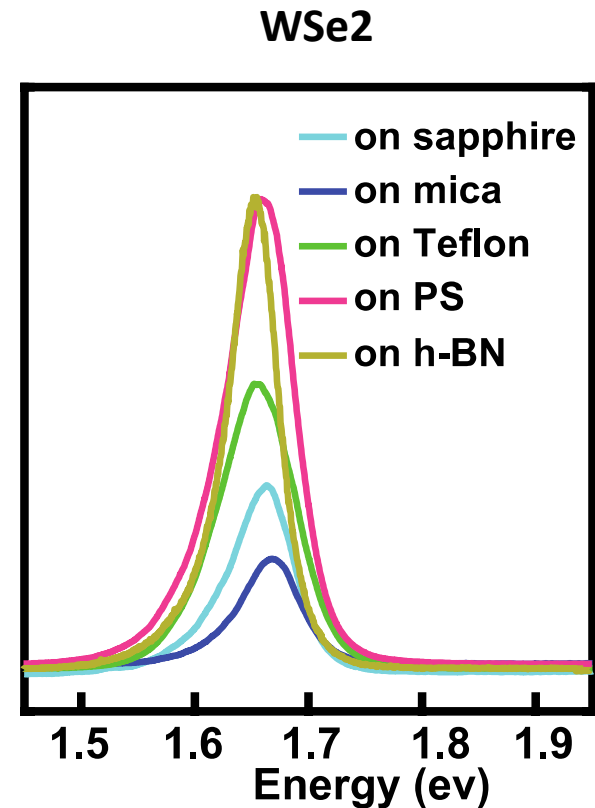


The doping effect of trapped moisture may cause more than one order of magnitude difference in PL.

Intrinsic Doping Effect of Substrates



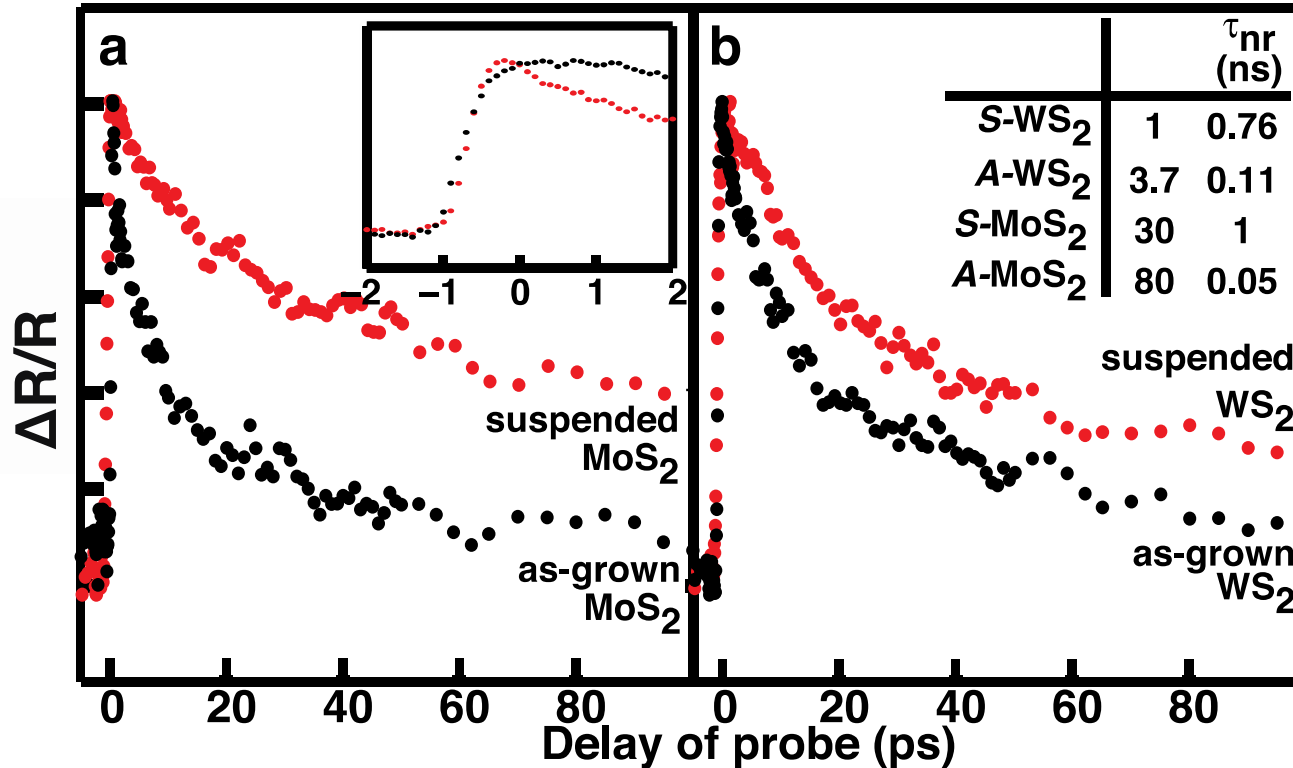
mica and Teflon best for WS₂ and MoS₂



Polystyrene and h-BN best for WSe₂.

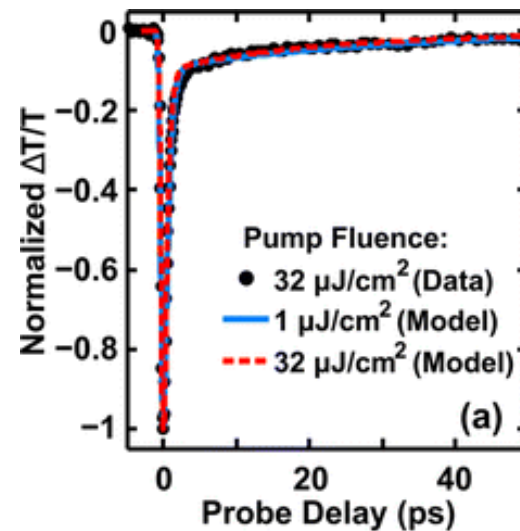
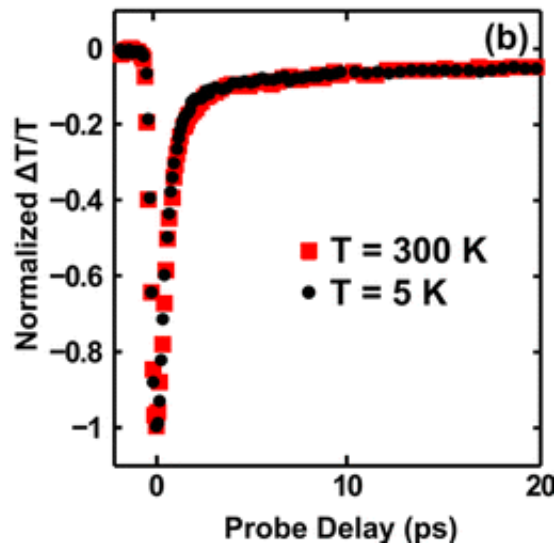
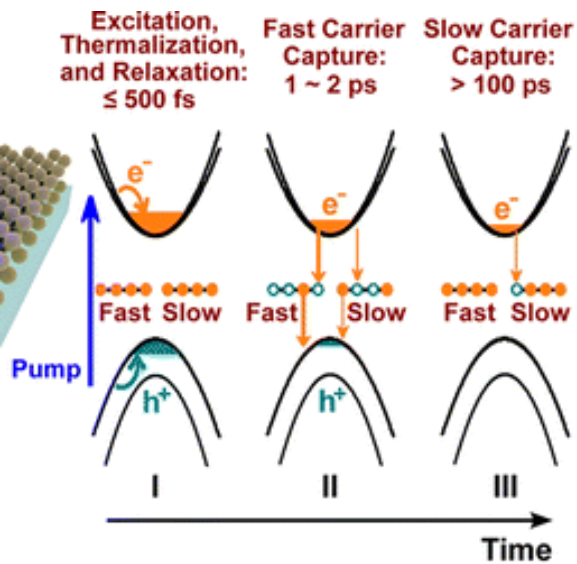
Substrates may also dope the monolayers, but much weaker than that of trapped moisture (by 2-4 times at maximum)

Defects of Substrates: Effect on Exciton Dynamics

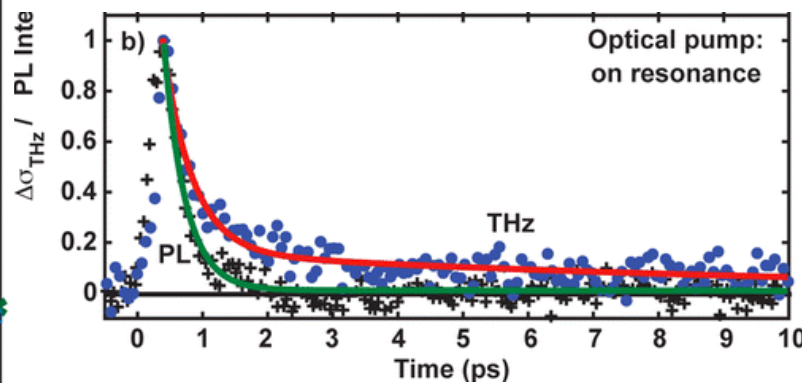
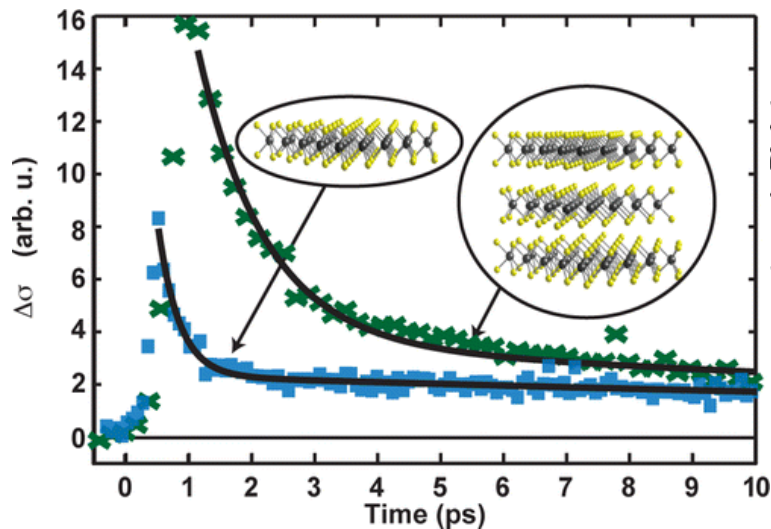


Substrate may facilitate non-radiative lifetime of excitons by providing defects to serve as recombination centers.

Exciton Dynamics: Defect-assisted



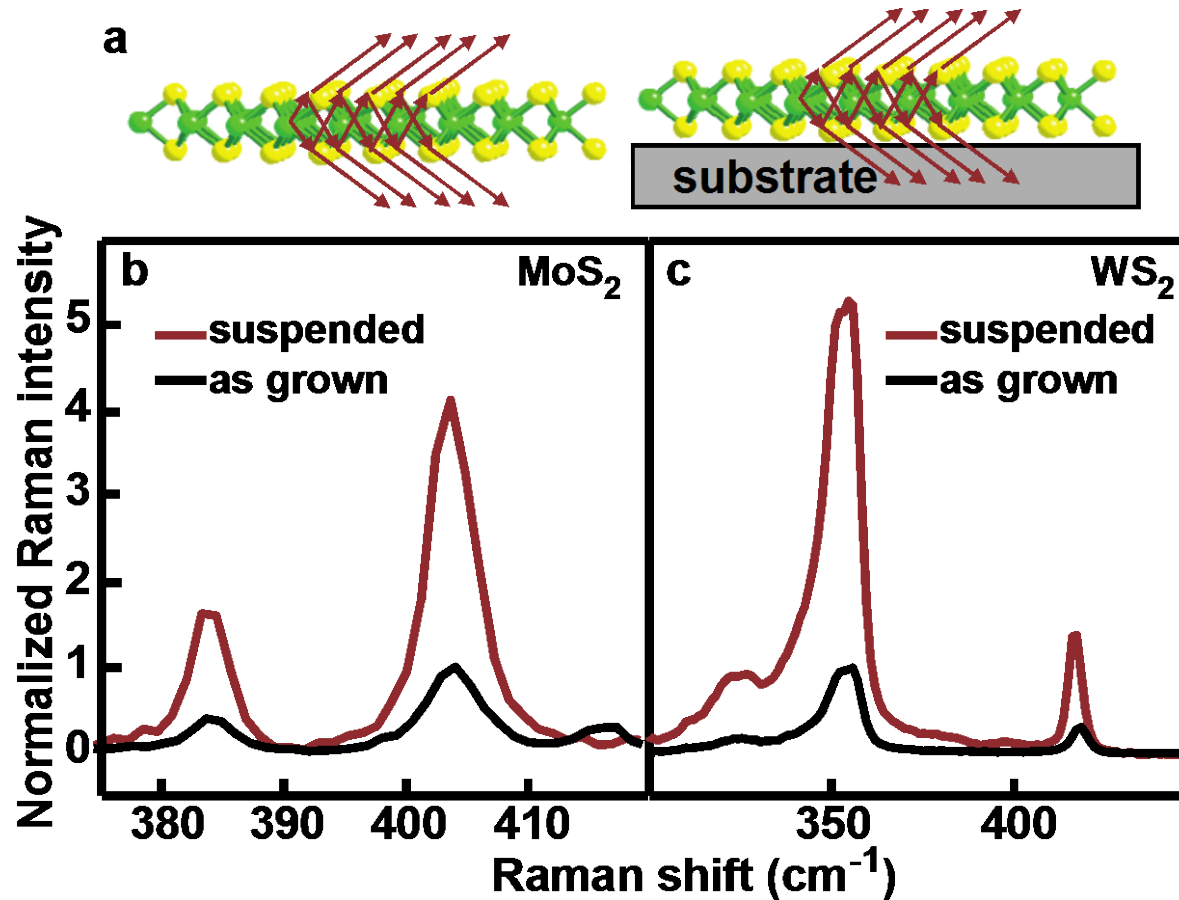
Nano Lett., 2015, 15 (1), pp 339–345



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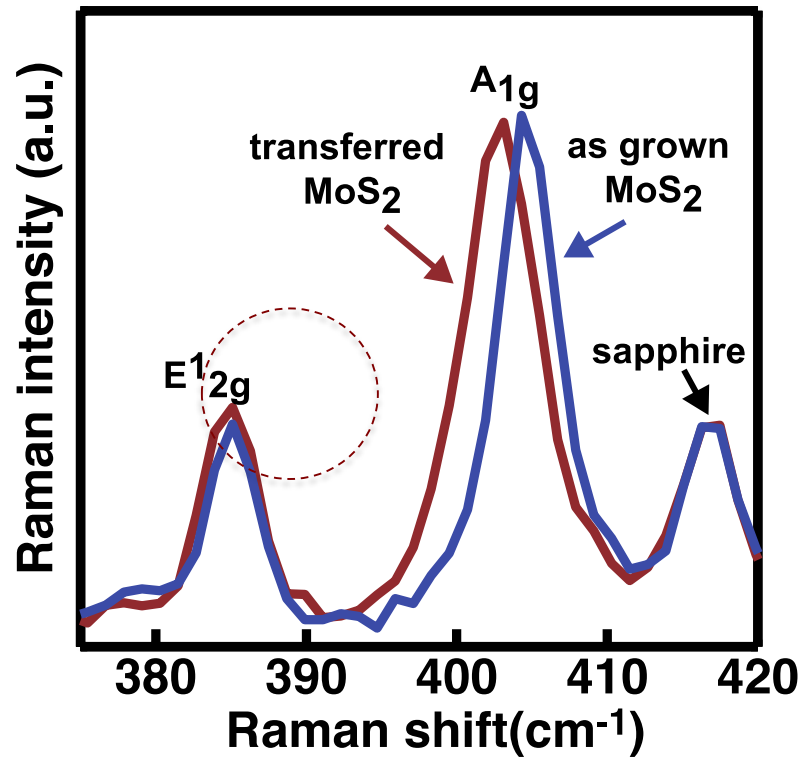
Defect-Assisted Electron–Hole Recombination

Index Contrast: Interference Effects

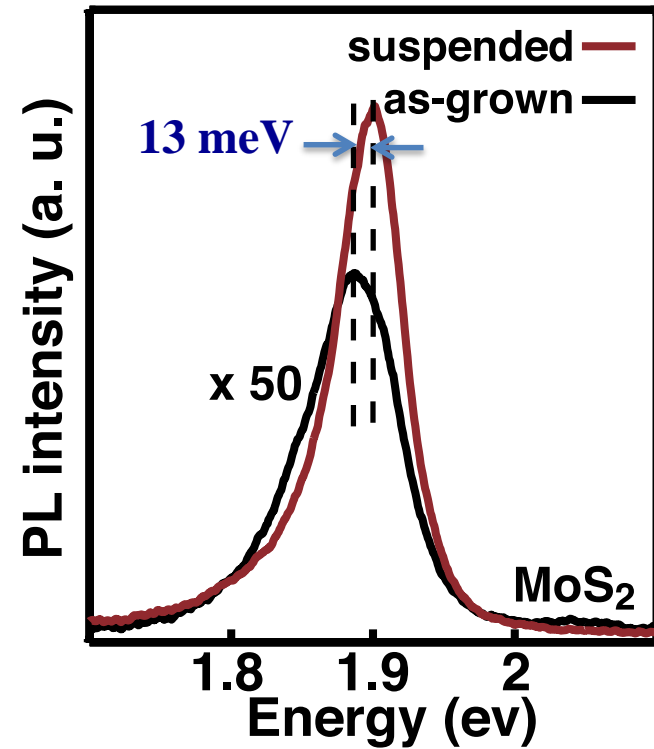


The interference effect of monolayers may affect the PL efficiency depending on the refractive index of the substrates.

Substrate-induced Strains & Dielectric Screening



The substrate-induced strain is small, $< 0.3\%$, affecting the PL efficiency $< 50\%$.

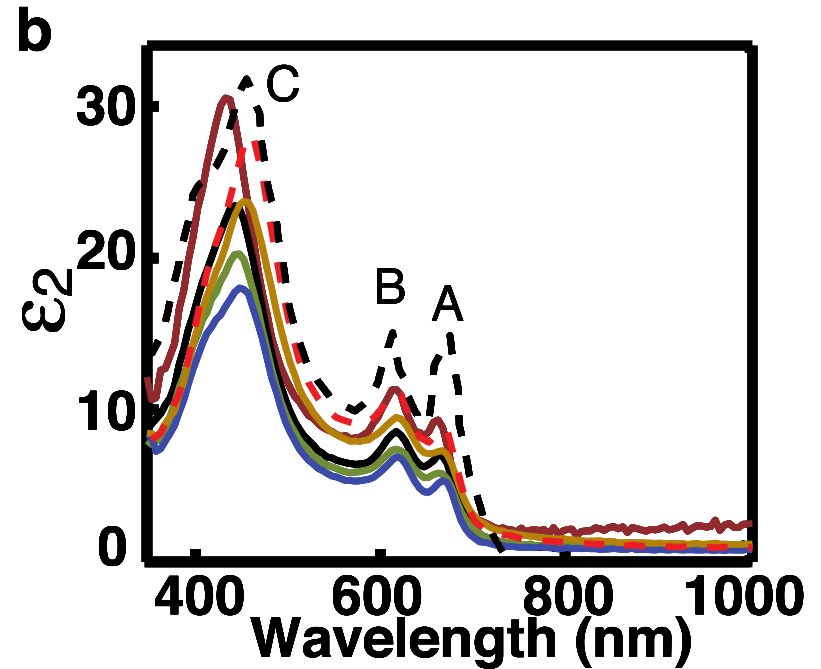
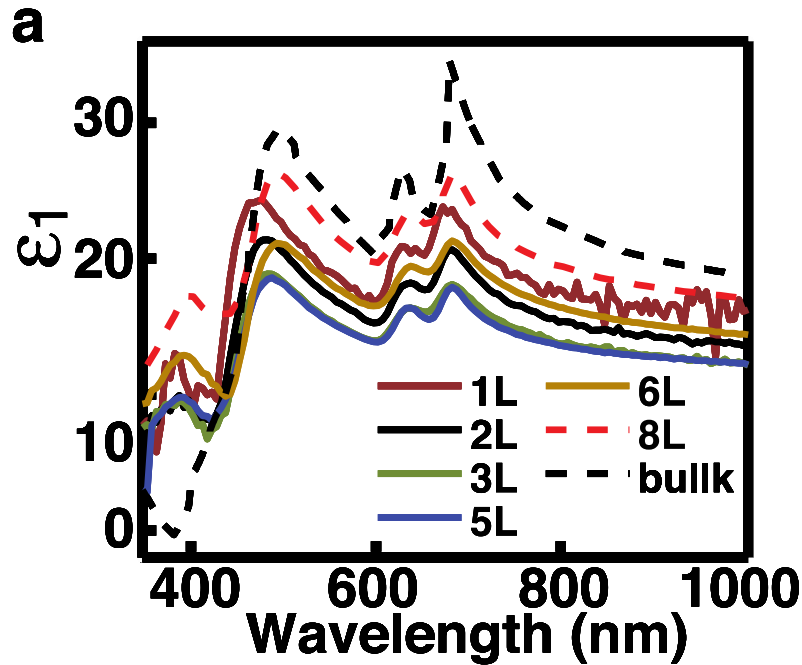
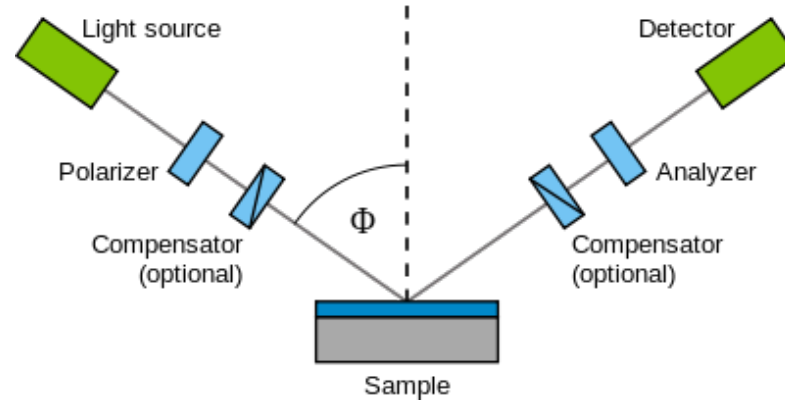


The effect of the substrate-induced dielectric screening on the PL < 2 times

Exciton-Dominated Light-Matter Interactions

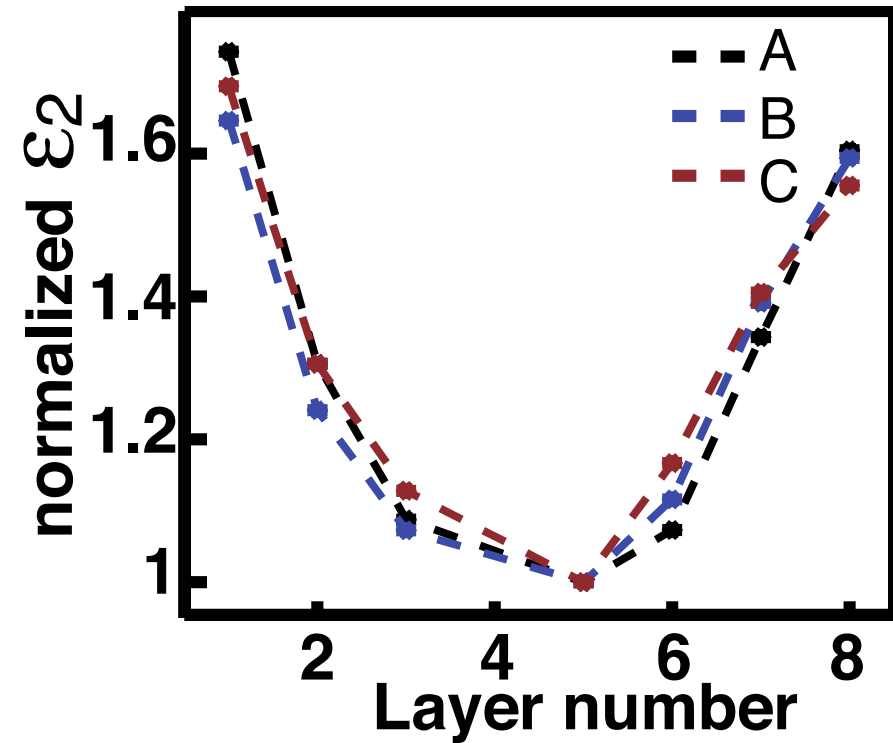
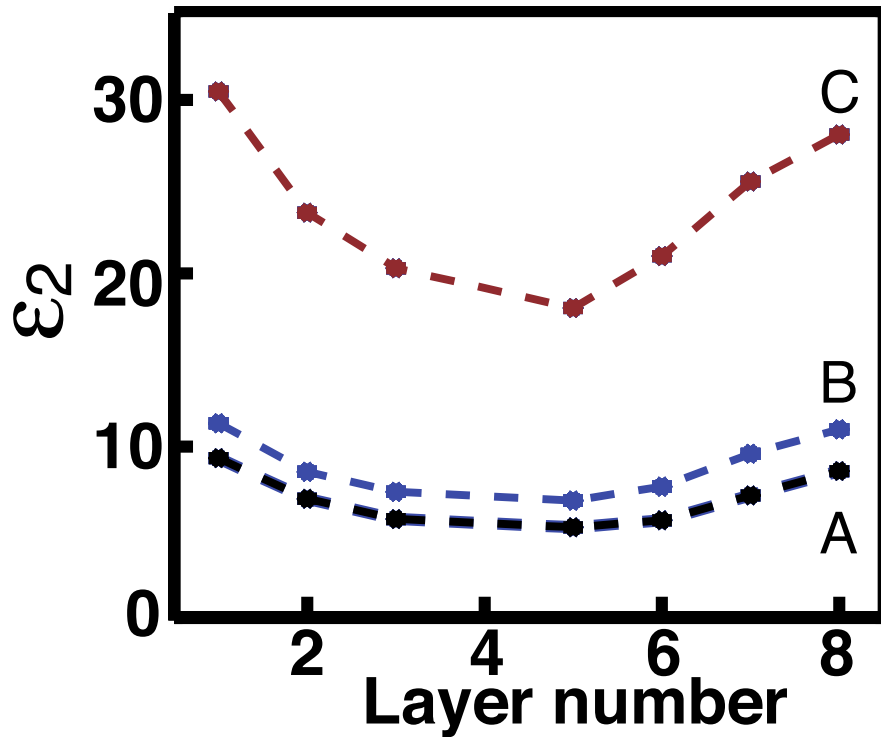
Layer-dependent Optical Constants

Ellipsometry measurement



2D MoS₂ exhibit an abnormal dependence on the layer number!

Layer-dependent Optical Constants



The layer-dependence of dielectric constant remains similar for the entire visible range.

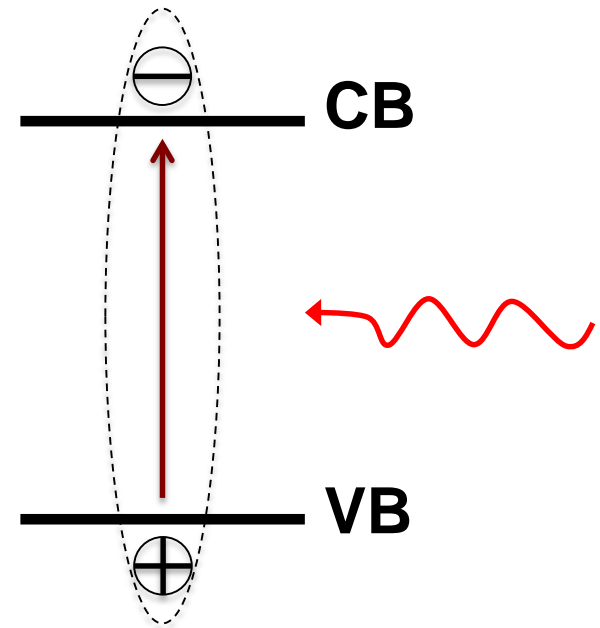
Physics of Dielectric Constant

$$\epsilon_{2,L}(\omega) = A_0 J_{cv,L} |U_L(0)|^2$$

A_0 a constant related with optical matrix element and transition bandwidth, which is layer-independent.

$J_{cv,L}$ joint density of the initial and final states involved in the transition

$U_L(0)$ the effect of excitons



Excitonic Effects

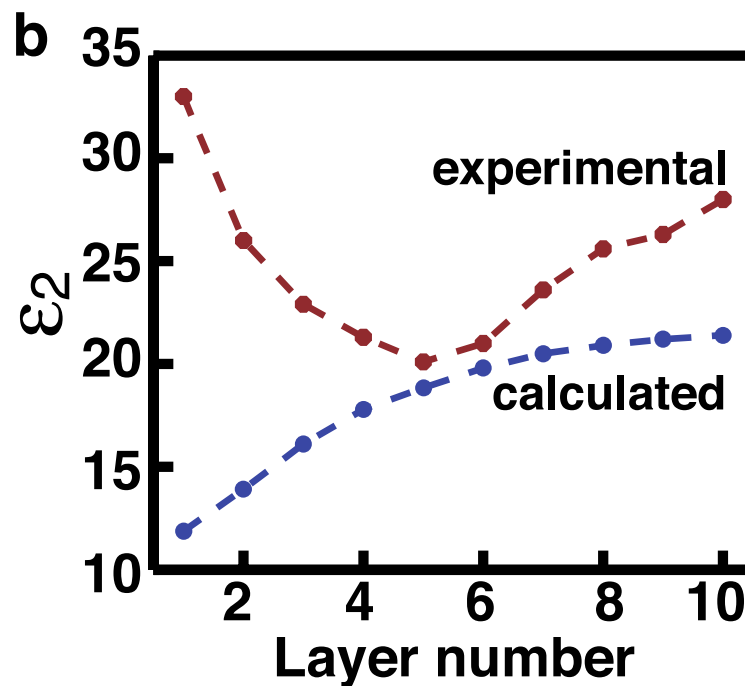
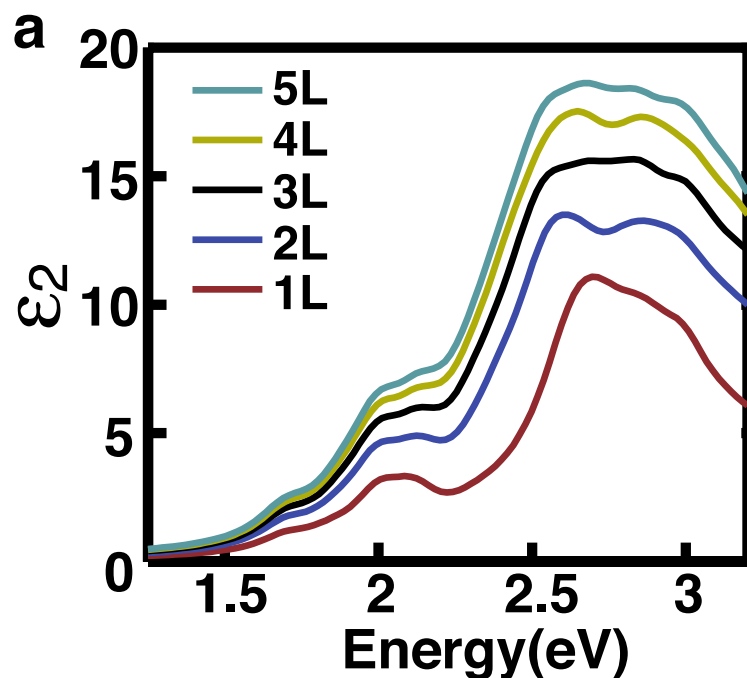
Conventional semiconductor:

$$\epsilon_{2,L}(\omega) = A_0 J_{cv,L}$$

Atomic thin MoS₂:

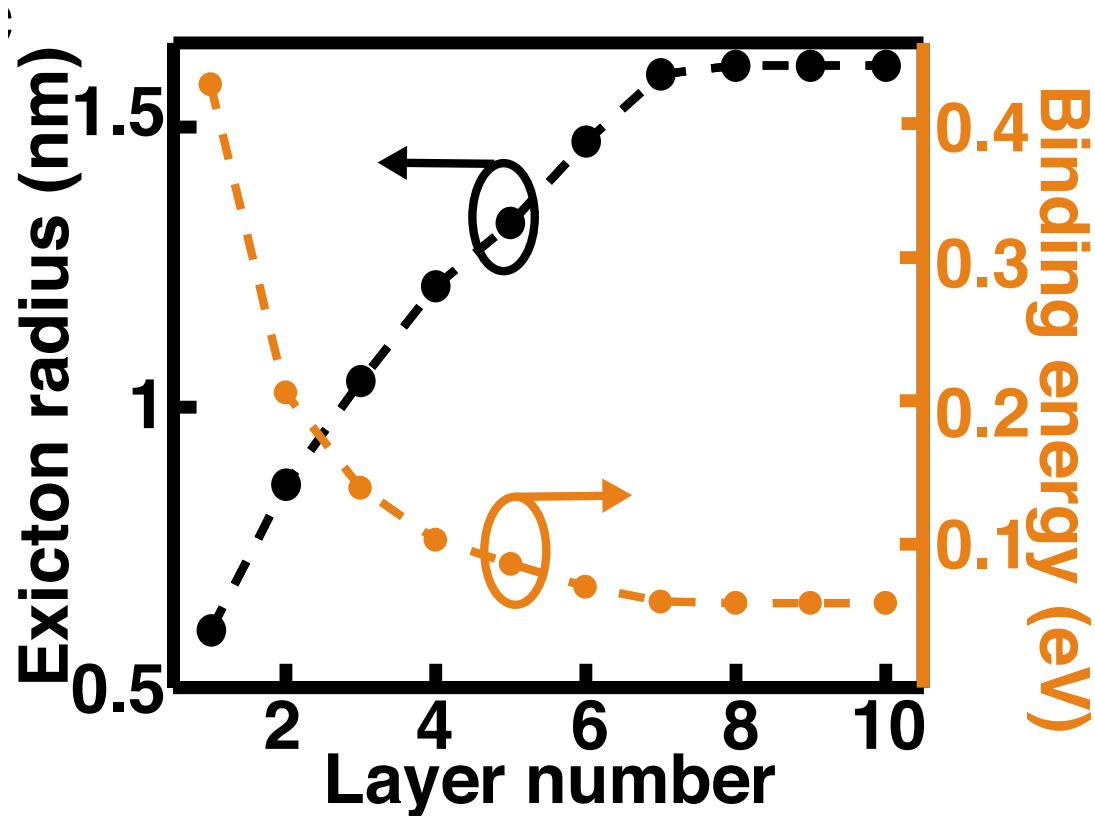
$$\epsilon_{2,L}(\omega) = A_0 J_{cv,L} |U_L(0)|^2$$

Excitonic effect



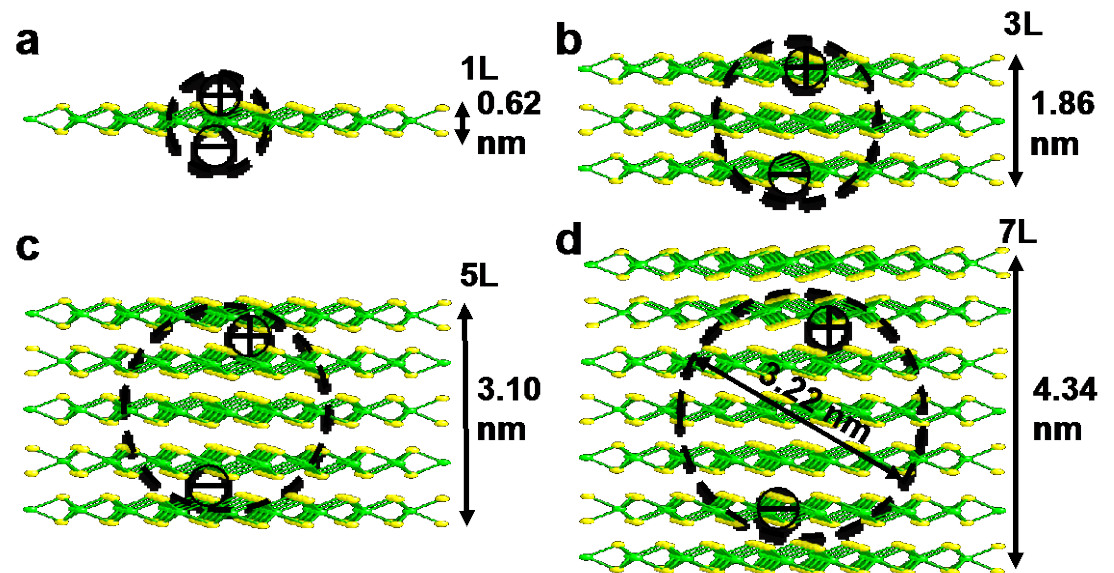
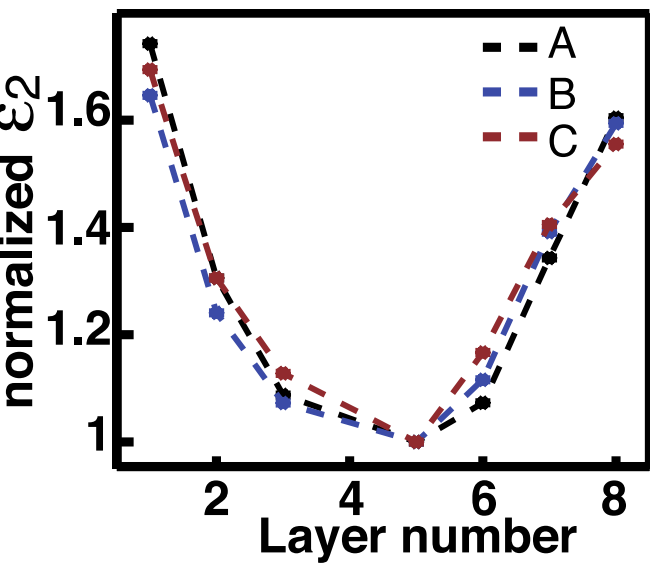
The excitonic effects dominates over the effect of the band structure.

Exciton Binding Energy and Exciton Radius



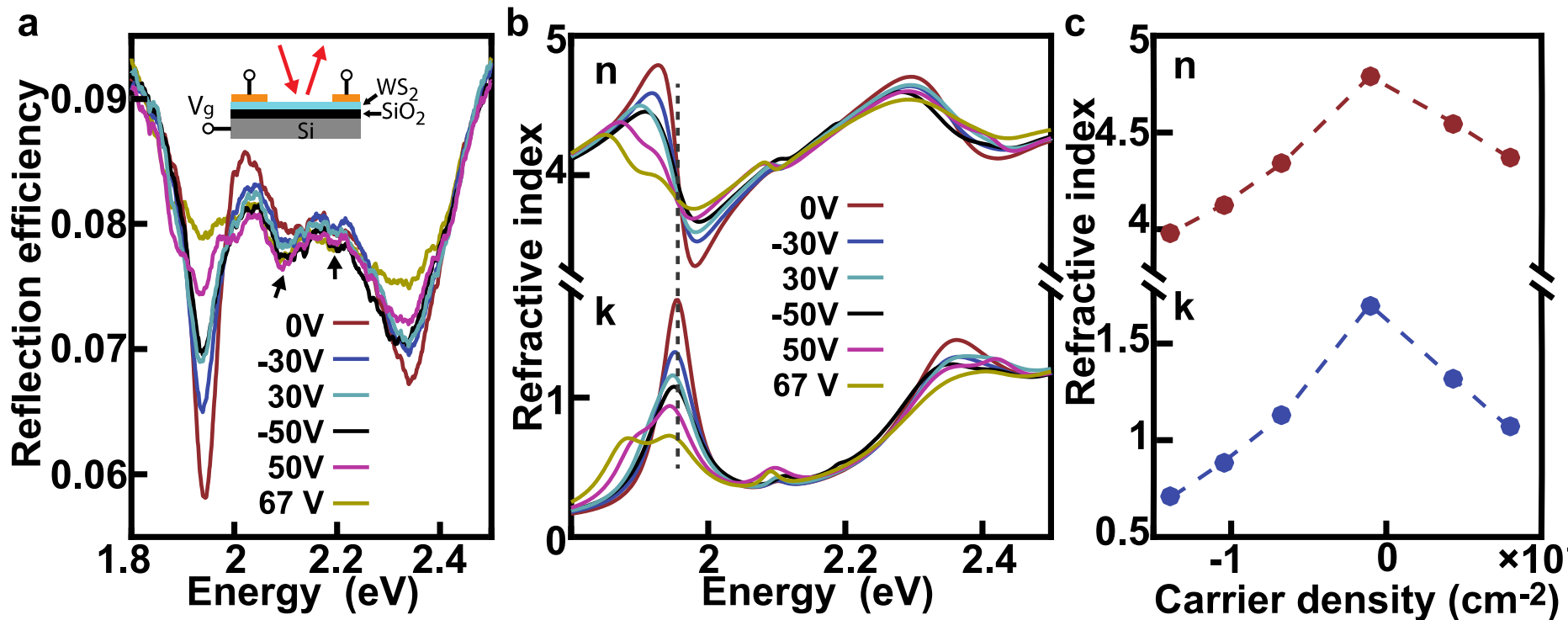
The experimental results are consistent with the theoretical calculations in references.

Geometric Confinement



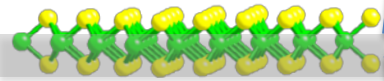
The excitation radius in bulk MoS₂ is 3.22 nm, close to the thickness of 5L films

Electrically Tunable Light-Matter Interactions: Field-Effect Photonics

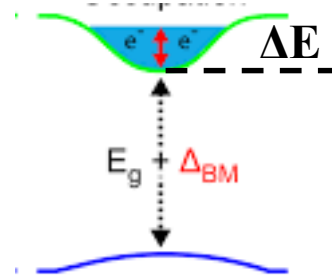


The refractive index can be tuned by > 60% with electrical gating!

Doping Effect



Phase Space Filling
(Pauli principle)

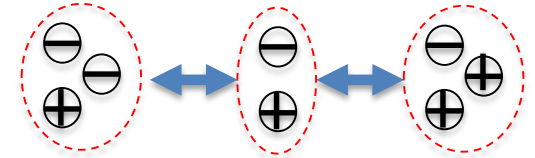


$$\Delta E = \pi \hbar^2 n / 2m$$

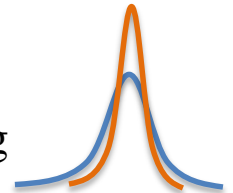
m: effective mass
n: density of charge

Coulomb scattering

Interchange of charged and neutral excitons

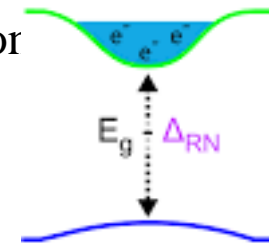


Dephasing: spectral broadening



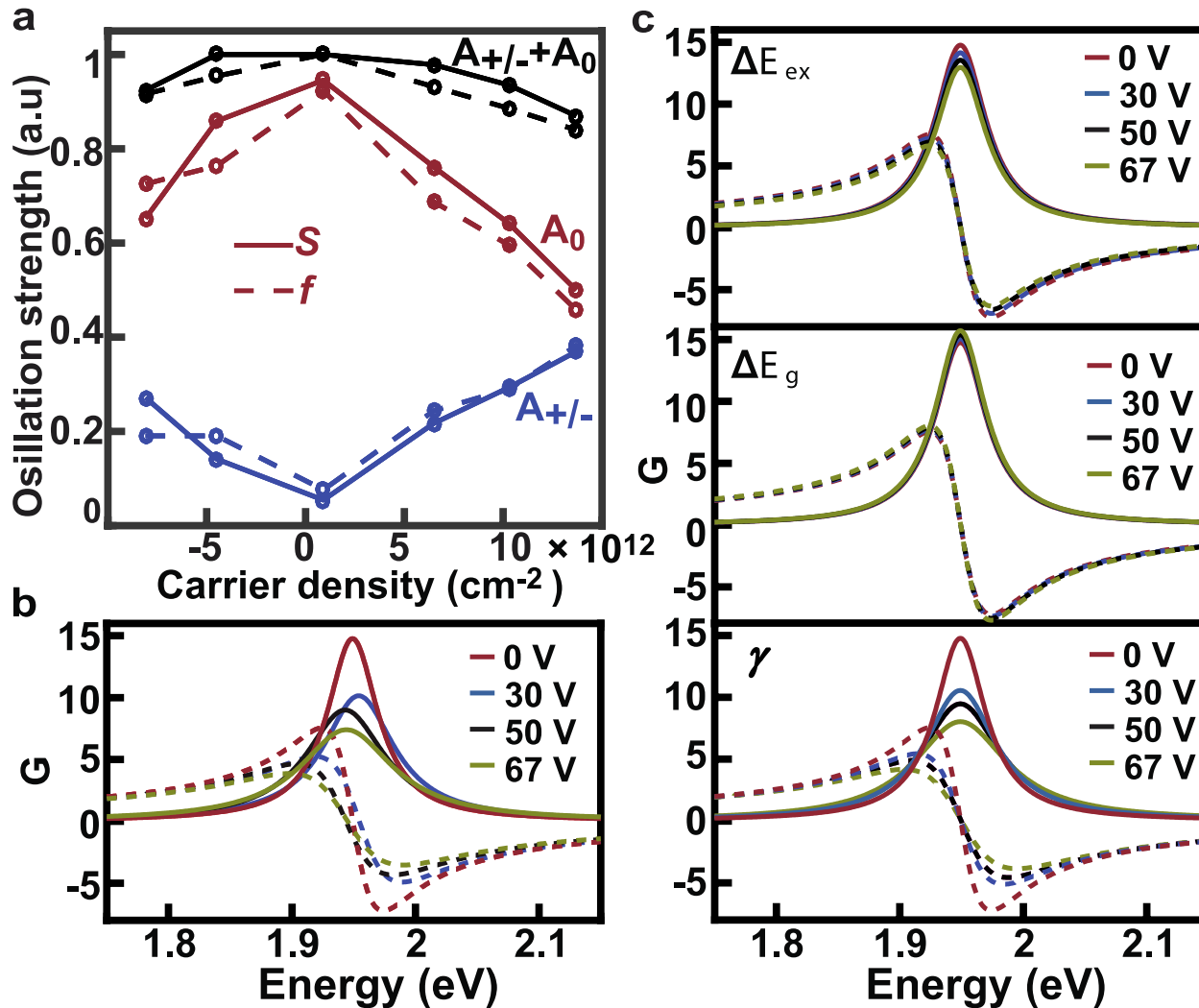
Dielectric screening
scattering

Bandgap renormalization



Change in exciton binding energy

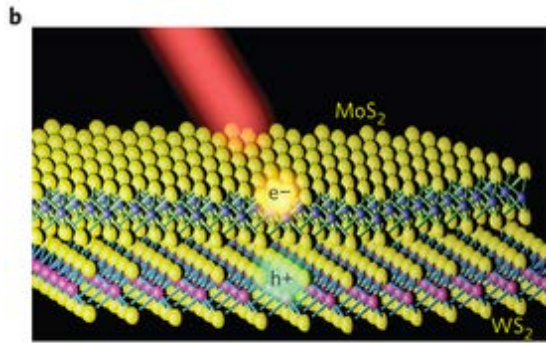
Electrically Tunable Light-Matter Interactions



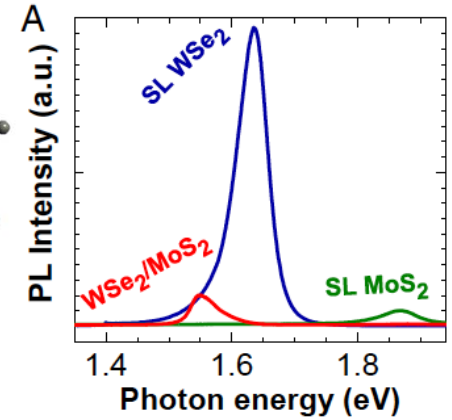
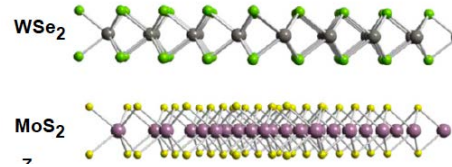
The dominant mechanism: interchange of trions and excitons and spectral broadening (Coulomb Scattering)

Exciton Engineering in Heterostructures

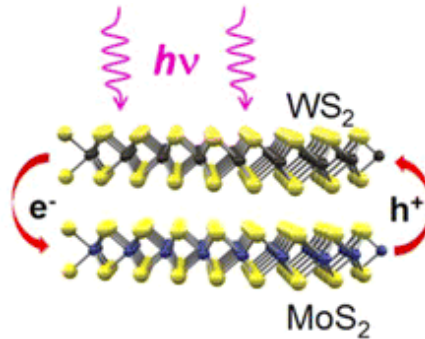
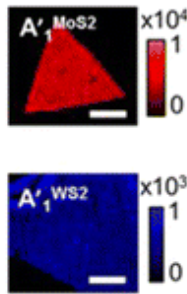
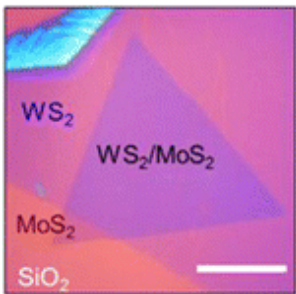
Exciton Dynamics in Heterostructures



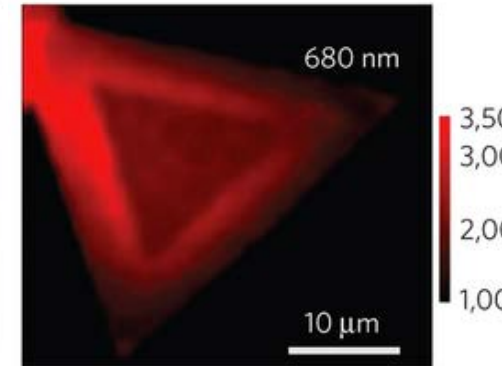
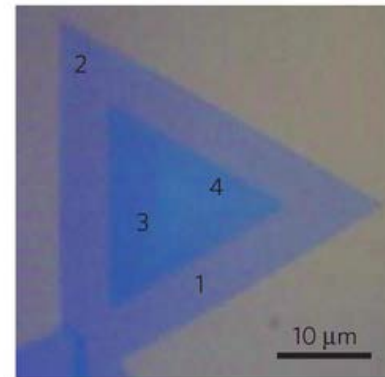
Nature Nanotechnology 9, 682–686 (2014)



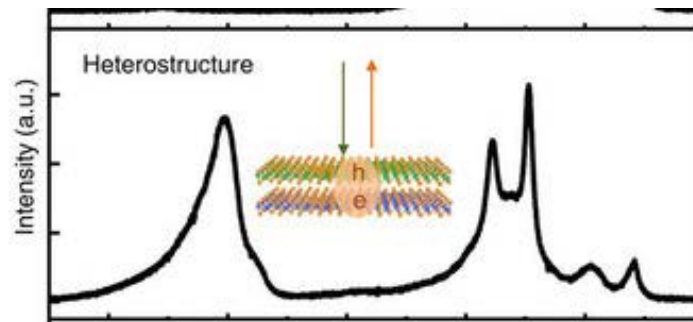
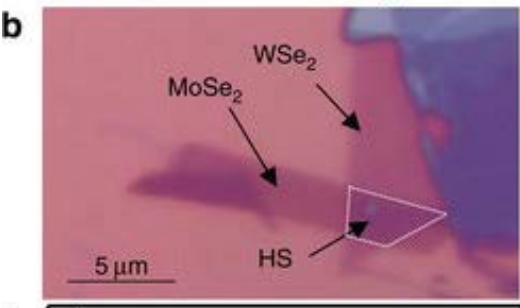
| PNAS | | vol. 111 | 6198–6202, 2014



Nano Lett., 2014, 14 (6), pp 3185–3190

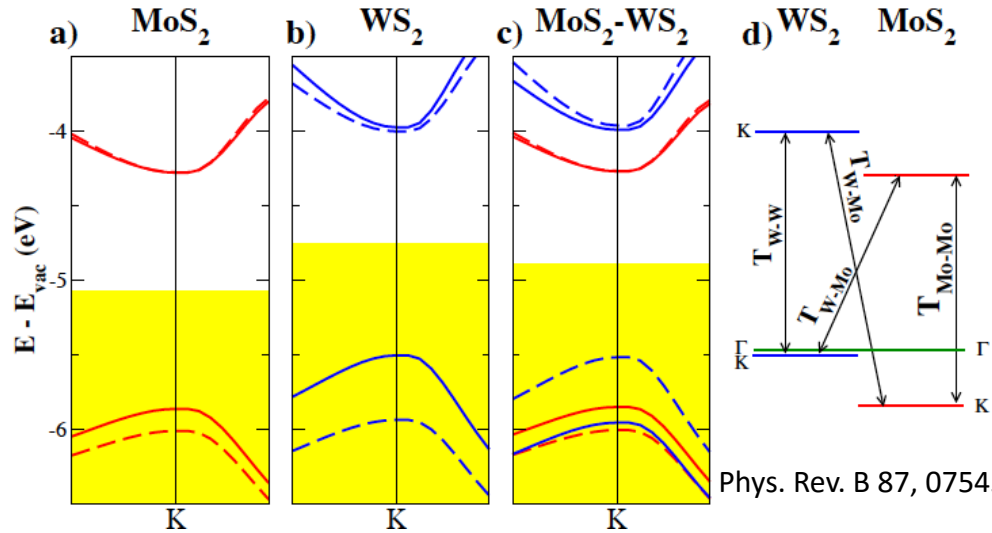


Nature Materials 13, 1135–1142 (2014)

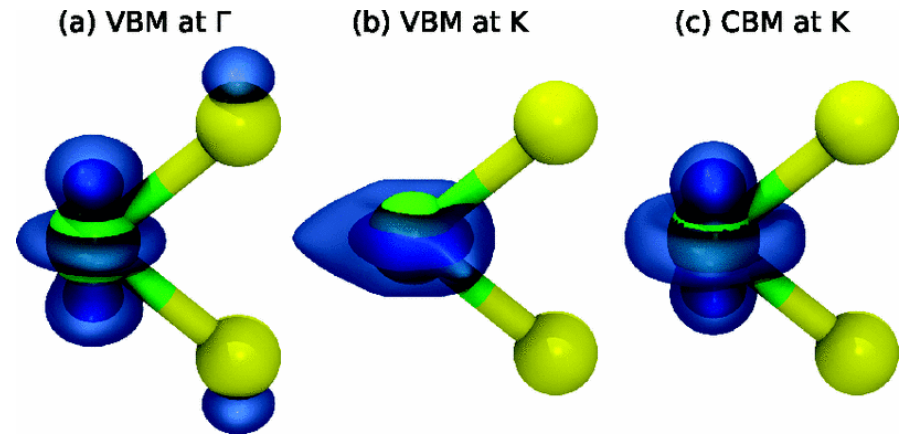
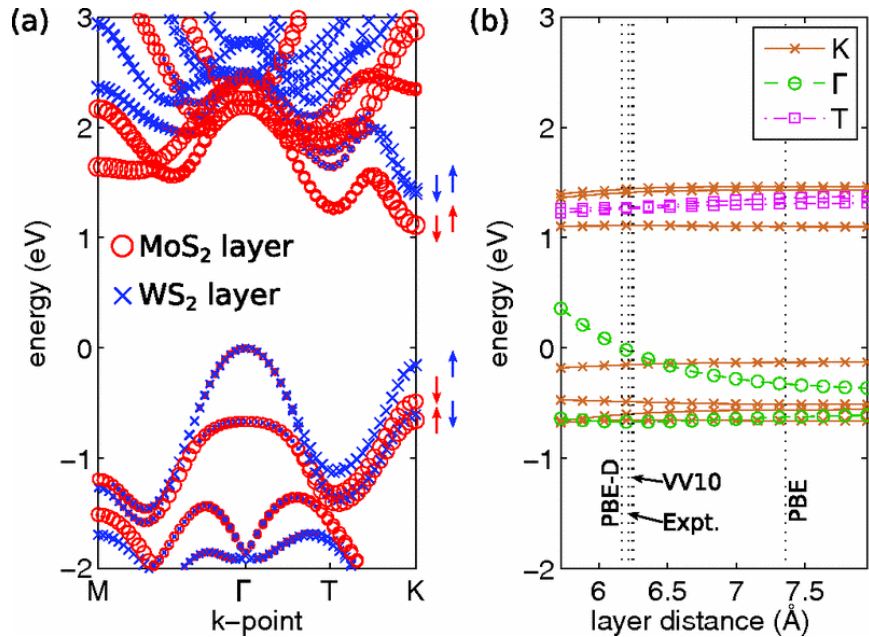


Nature Communications 6, Article number: 6242

Band Structures in MoS₂/WS₂ Heterostructures

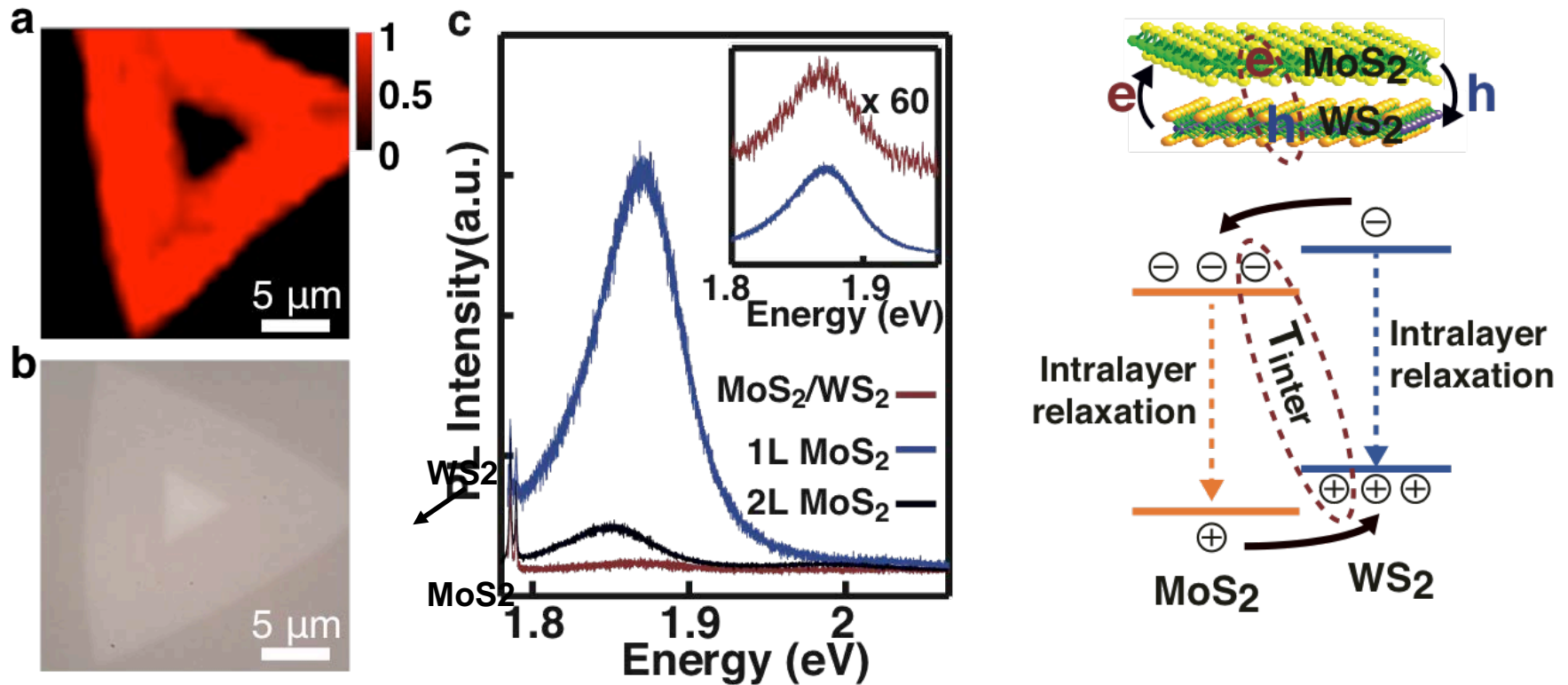


Phys. Rev. B 87, 075451 (2013)



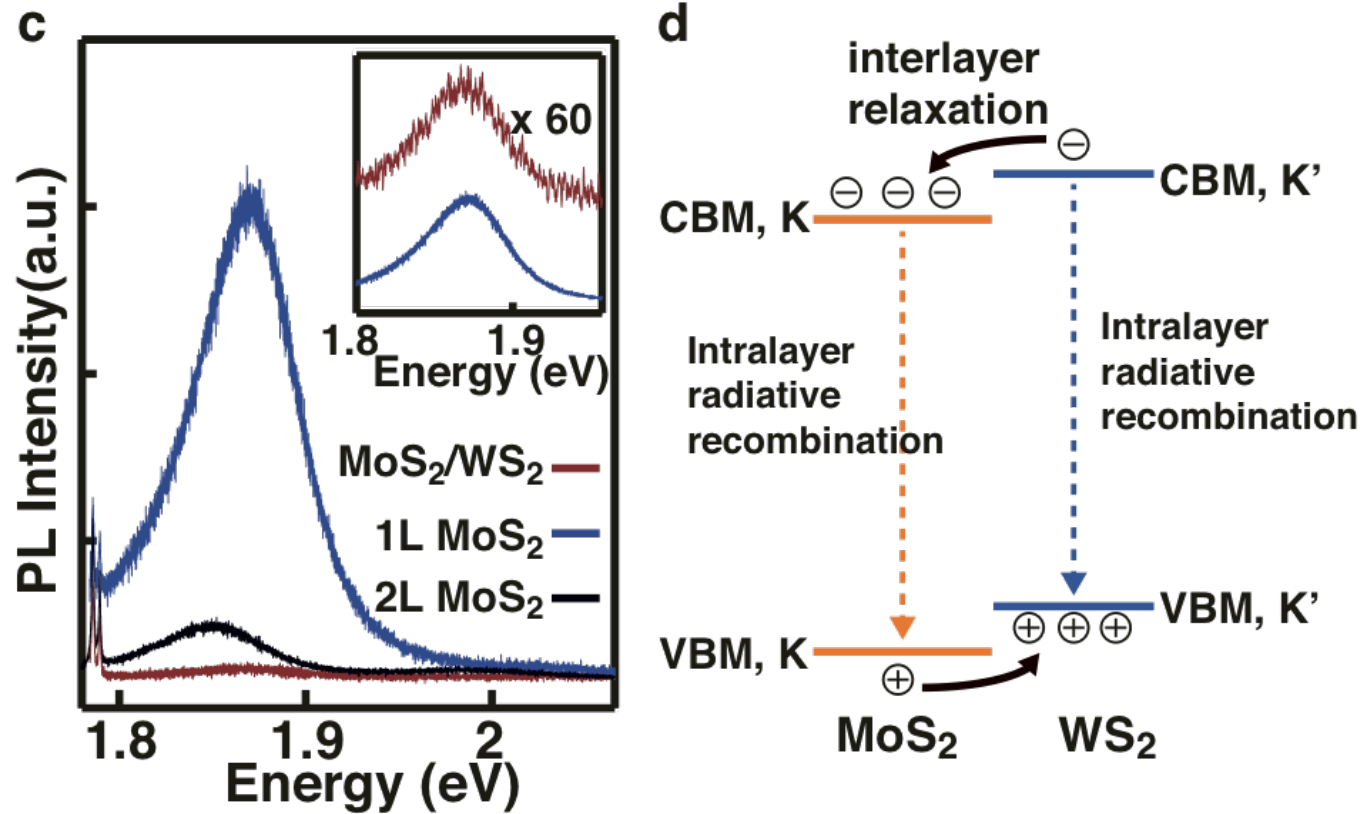
Phys. Rev. B 88, 085318

Equally Efficient Interlayer Charge Transfer in Epitaxial and Non-epitaxial MoS₂/WS₂ Heterostructures



The PL in MoS₂/WS₂ is two orders of magnitude less!

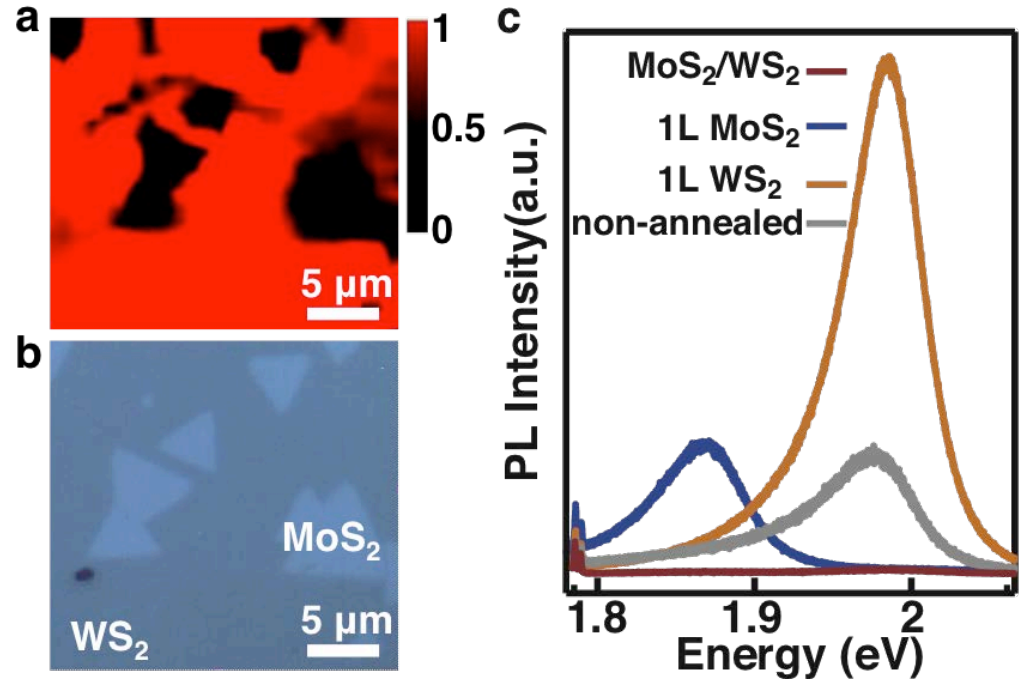
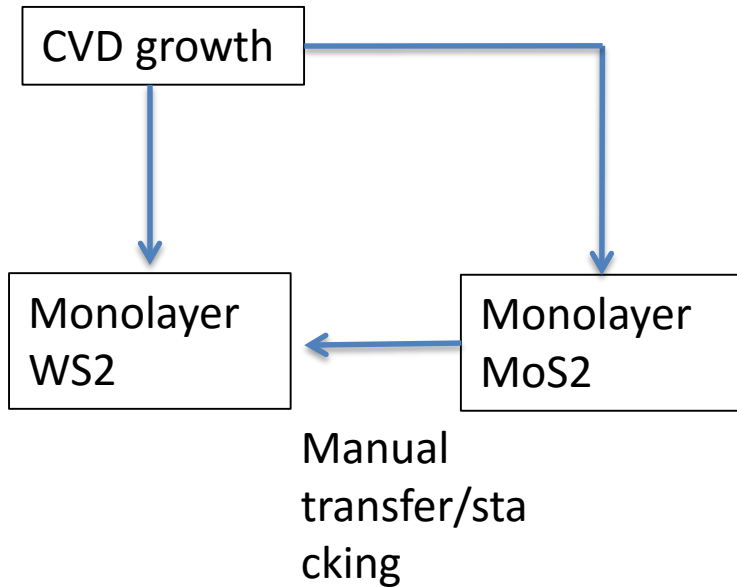
Efficient Interlayer Exciton Relaxation



- The radiative lifetime of excitons in MoS₂ is around 1-5 ps.
- The PL is suppressed by 50 - 100 times after the heterostructuring.

The interfacial charge transfer is in scale of 10-100 fs!

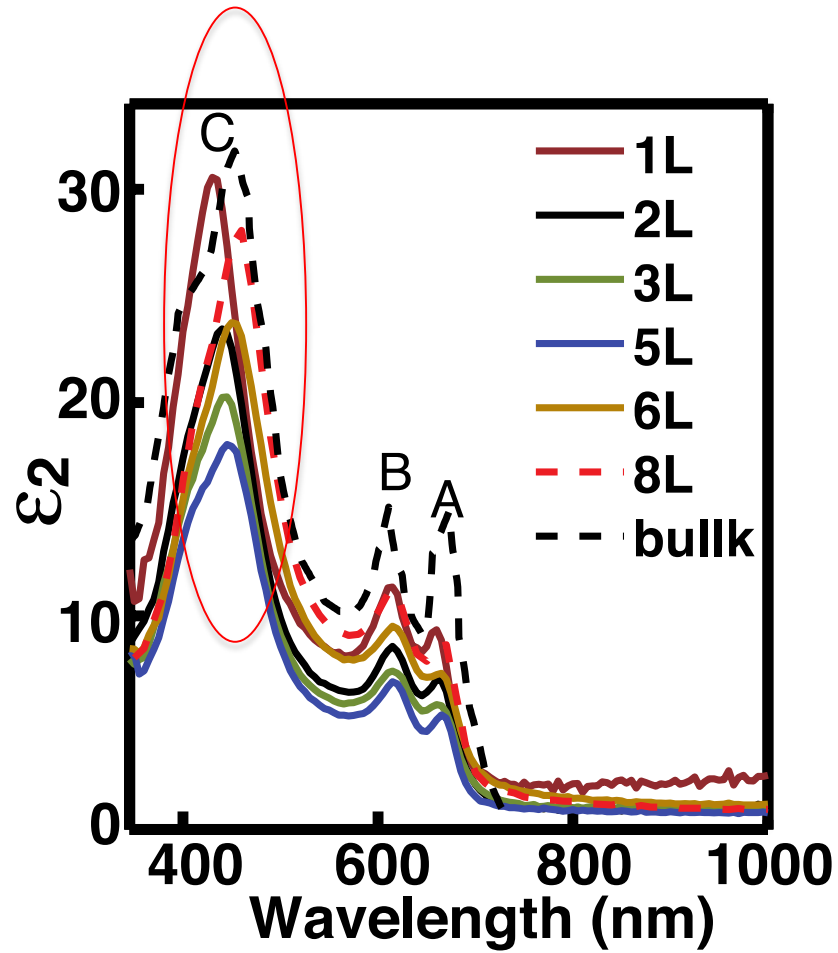
Equally Efficient Interlayer Charge Transfer in Epitaxial and Non-epitaxial MoS₂/WS₂ Heterostructures



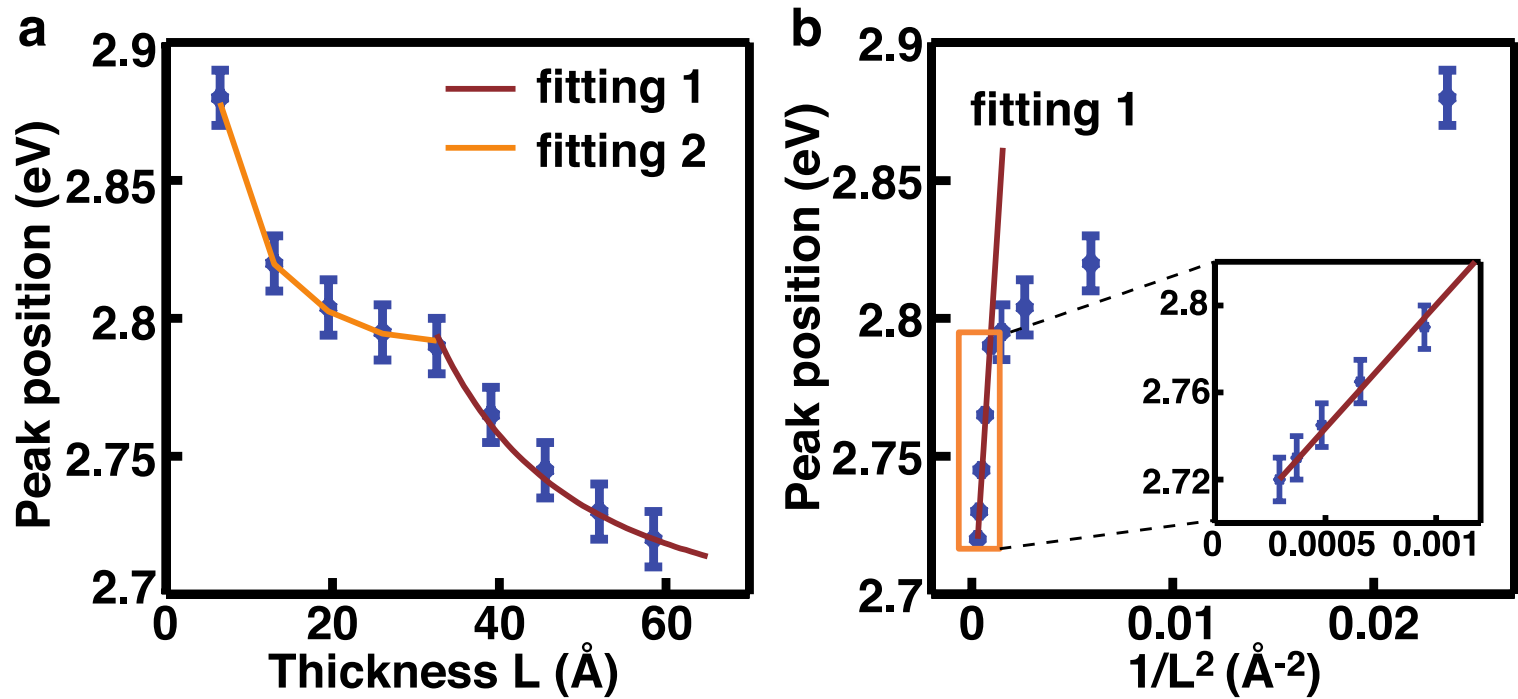
Efficient interlayer relaxation in non-epitaxial heterostructures!

Thank You!

Layer-dependent Peak Positions: Excitonic Effects



Layer-dependent Exciton Binding Energy



Model 1. conventional quantum confinement, which assumes a constant excitonic binding energy

$$E = E_g + \pi^2 \hbar^2 / (2m_{\text{eff}} L^2)$$

Model 2 based on quantum confinement in fractional space. It assumes the excitonic binding energy varies.